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(54) **LIGHT-EMITTING ELEMENT UNIT AND
DISPLAY DEVICE**

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(2013.01)

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See application file for complete search history.

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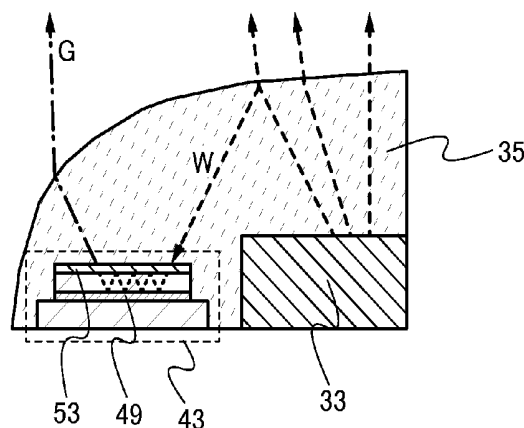
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(57) **ABSTRACT**

A light-emitting element unit which can improve color purity
of light emitted from a color filter is provided. A display
device with high color purity and high color reproducibility is
provided. The light-emitting element unit includes a wiring
board, a light-emitting element chip provided over the wiring
board, a micro optical resonator provided over the wiring
board and at the periphery of the light-emitting element chip,
and a phosphor layer covering the light-emitting element chip
and the micro optical resonator. The display device includes a
display panel having a coloring layer and a backlight module
having the light-emitting element unit. Examples of the dis-
play panel include: a liquid crystal panel; and a display panel
including an opening portion provided over a first substrate,
MEMS moving over the opening portion in the lateral direc-
tion, and a second substrate provided with a coloring layer in
a portion corresponding to the opening portion.

23 Claims, 15 Drawing Sheets



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FIG. 1A

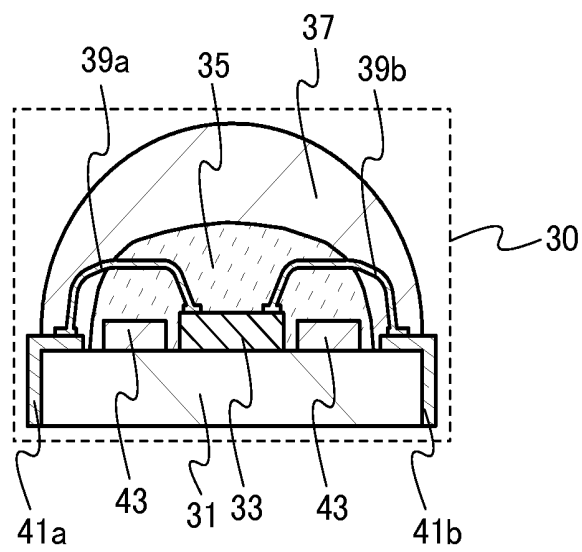


FIG. 1B

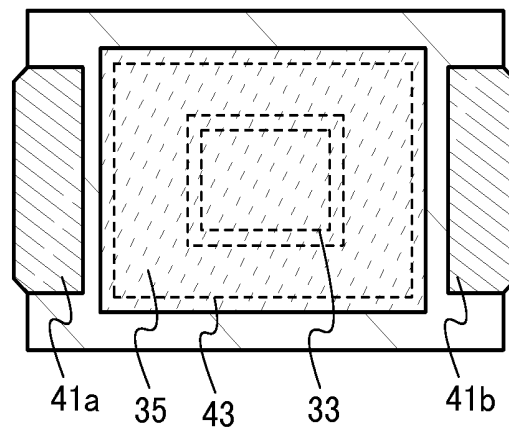


FIG. 2A-1

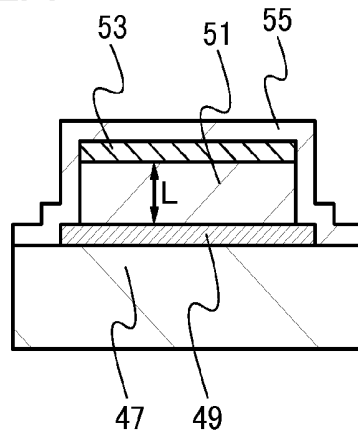


FIG. 2A-2

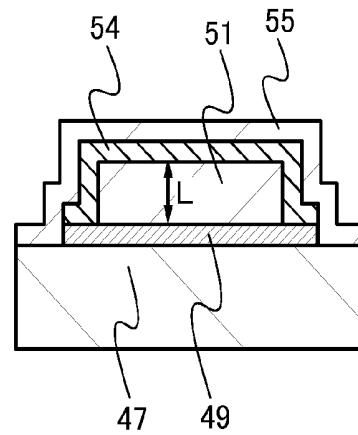


FIG. 2B

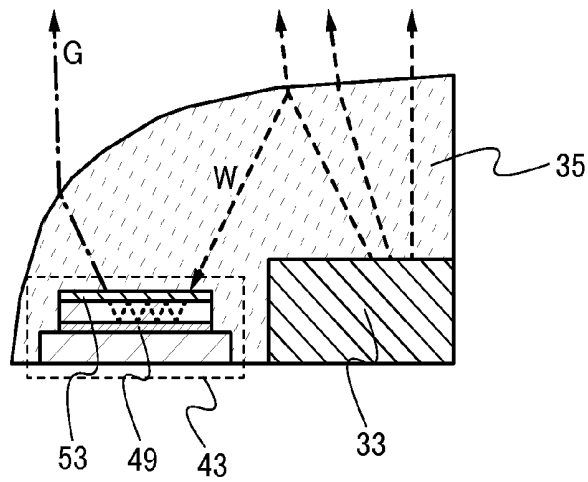


FIG. 2C

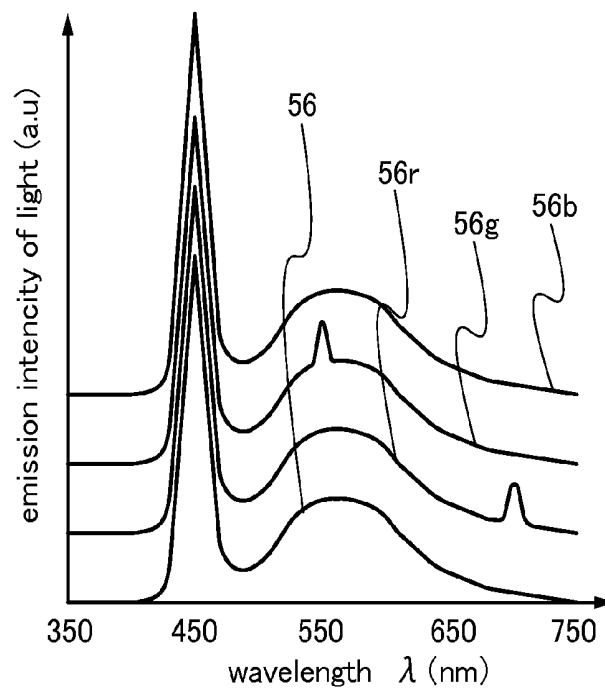


FIG. 3

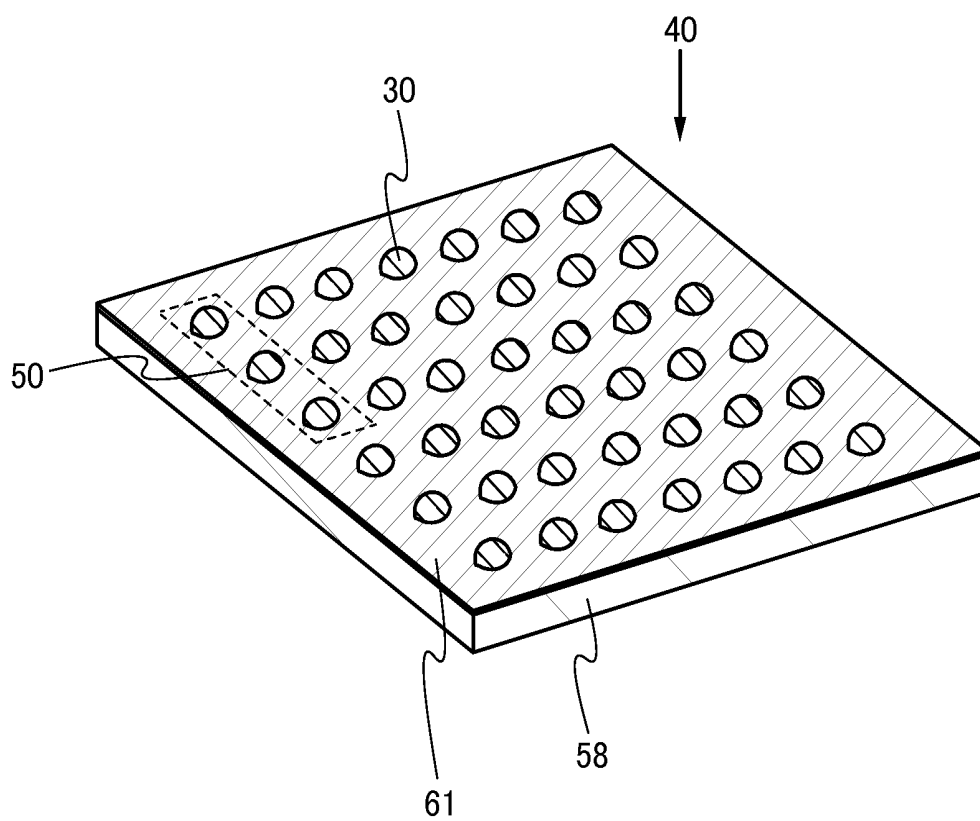


FIG. 4

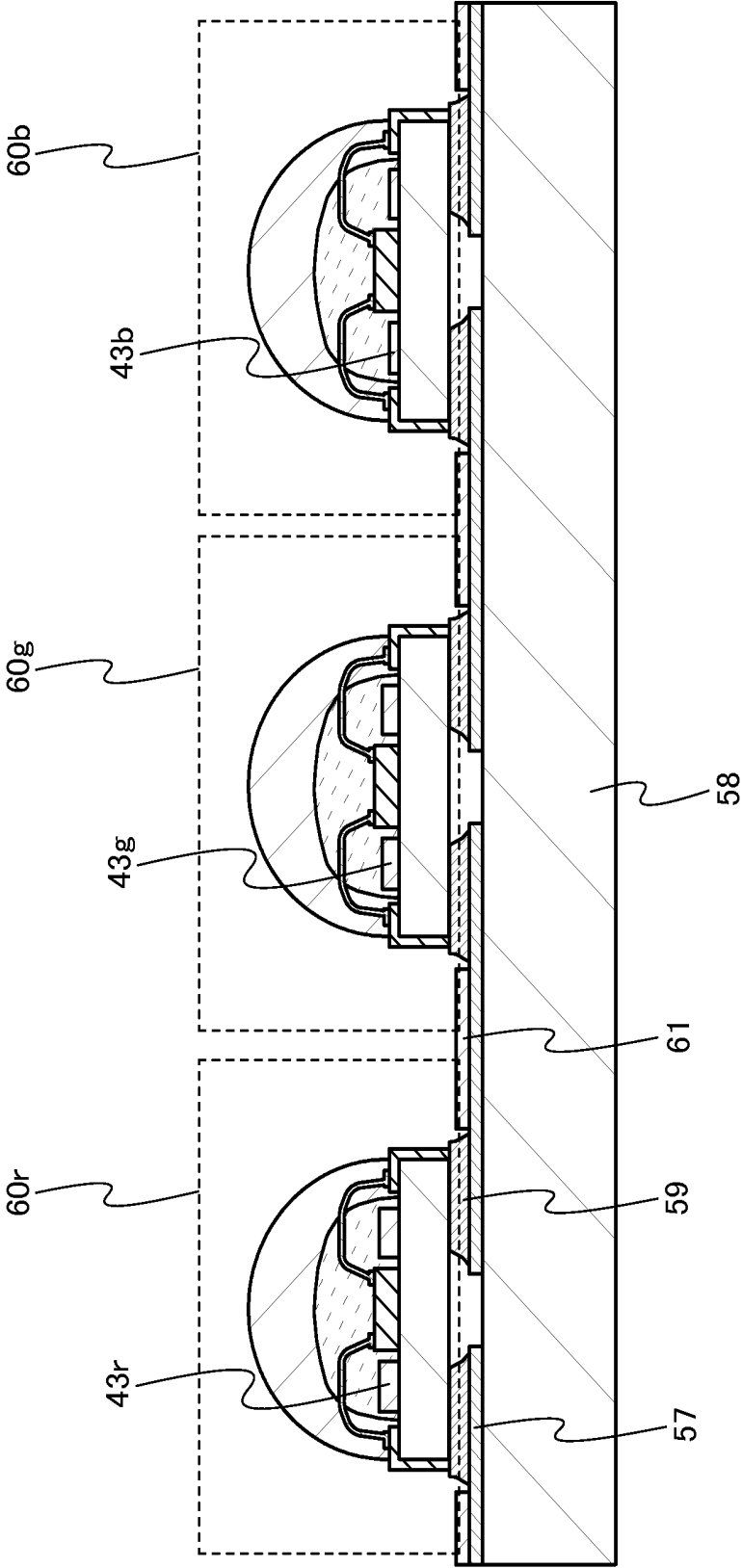


FIG. 5

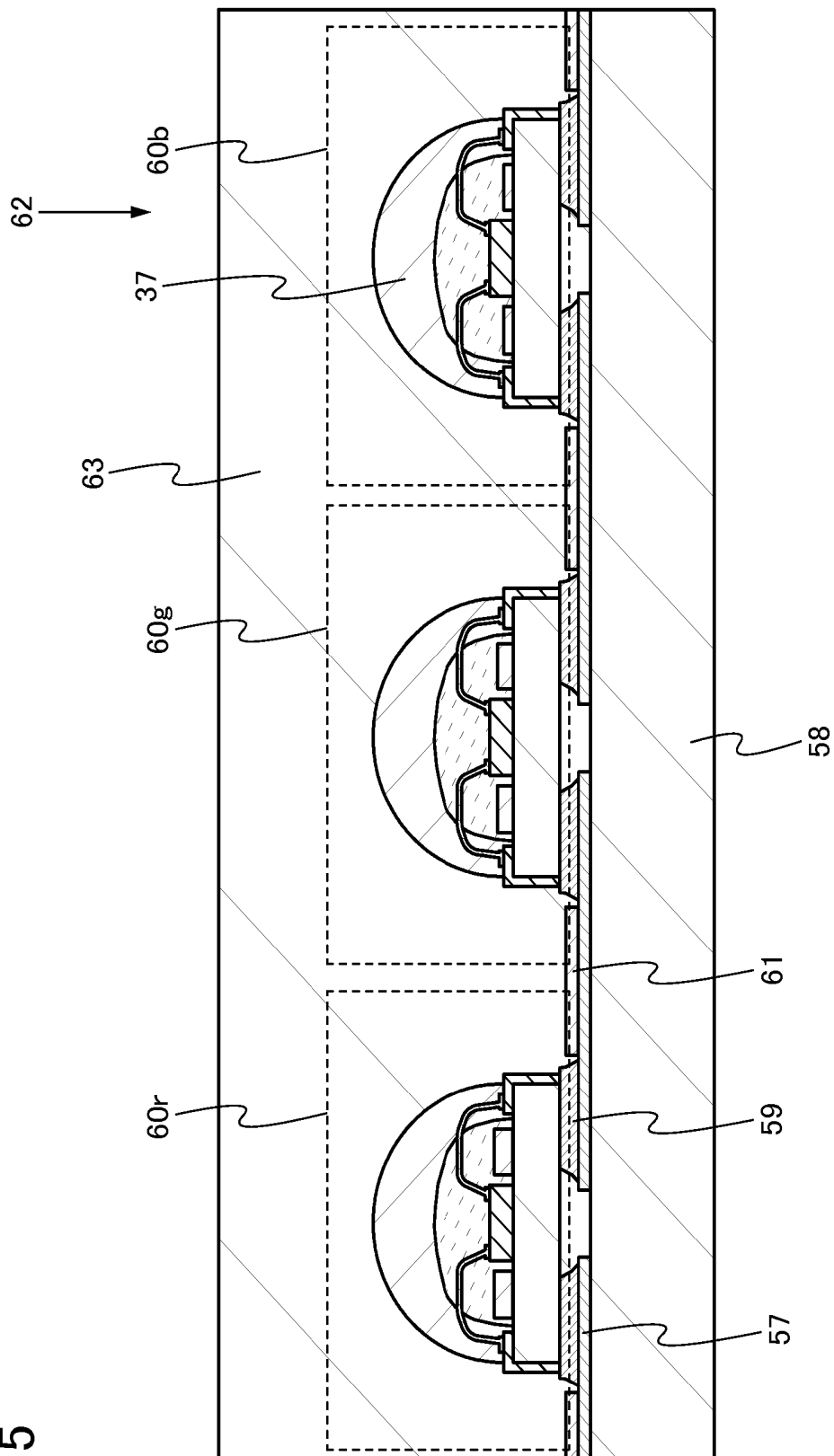


FIG. 6A

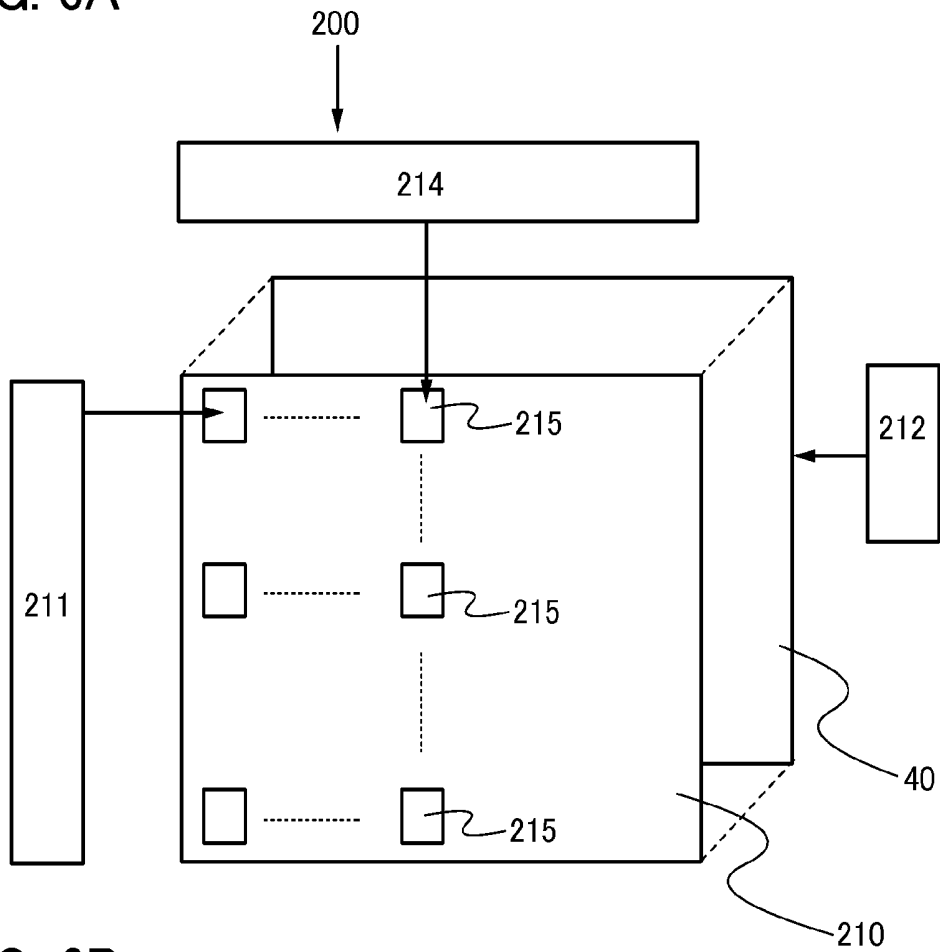


FIG. 6B

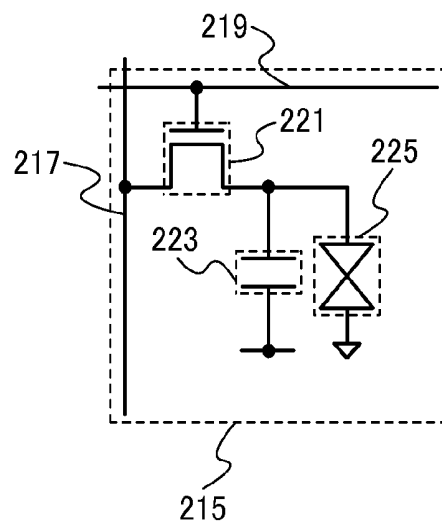


FIG. 7A

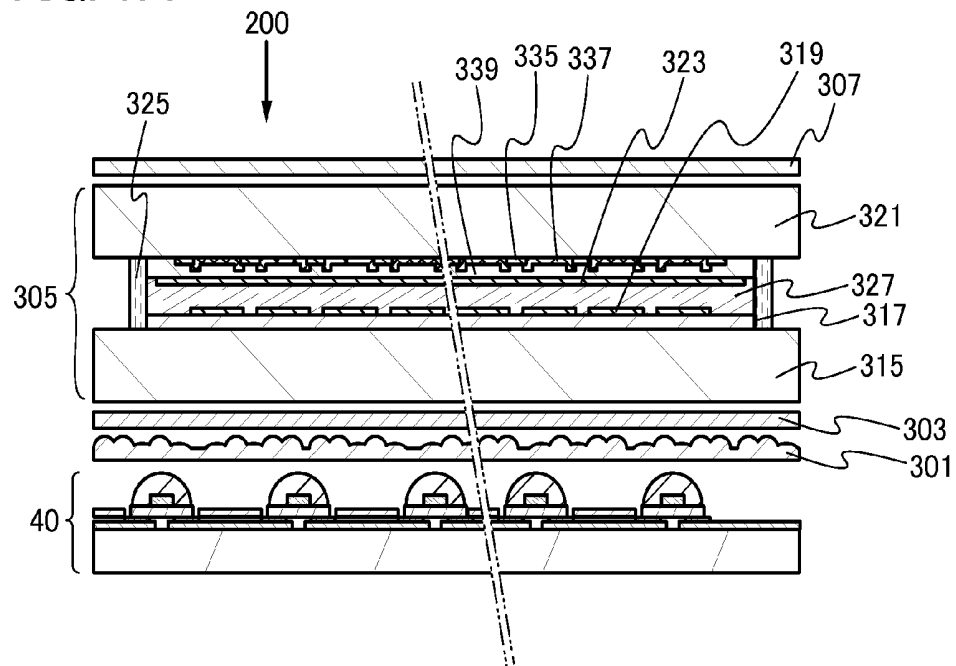


FIG. 7B

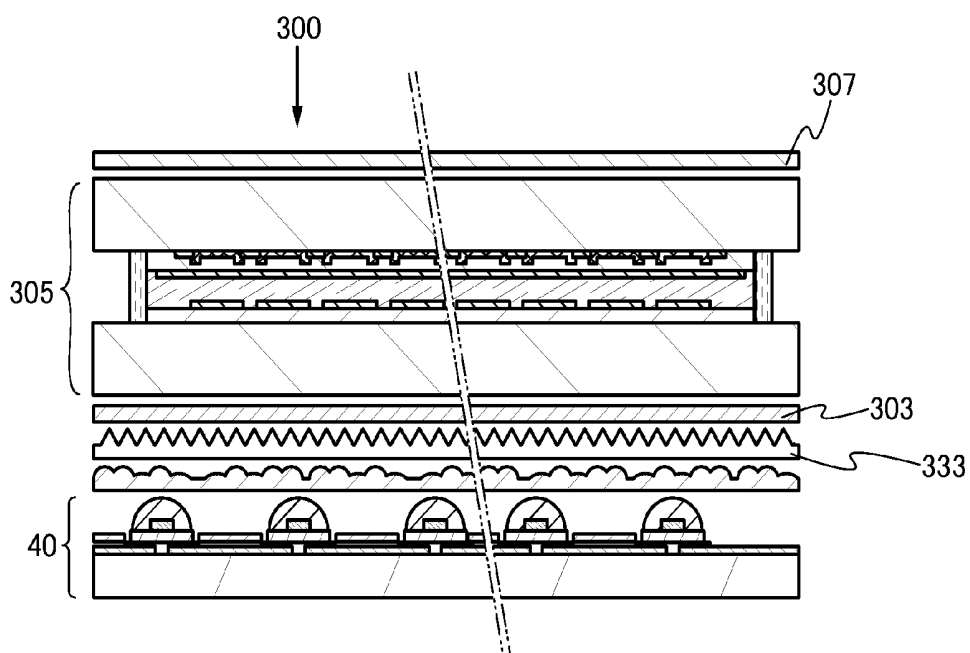


FIG. 8

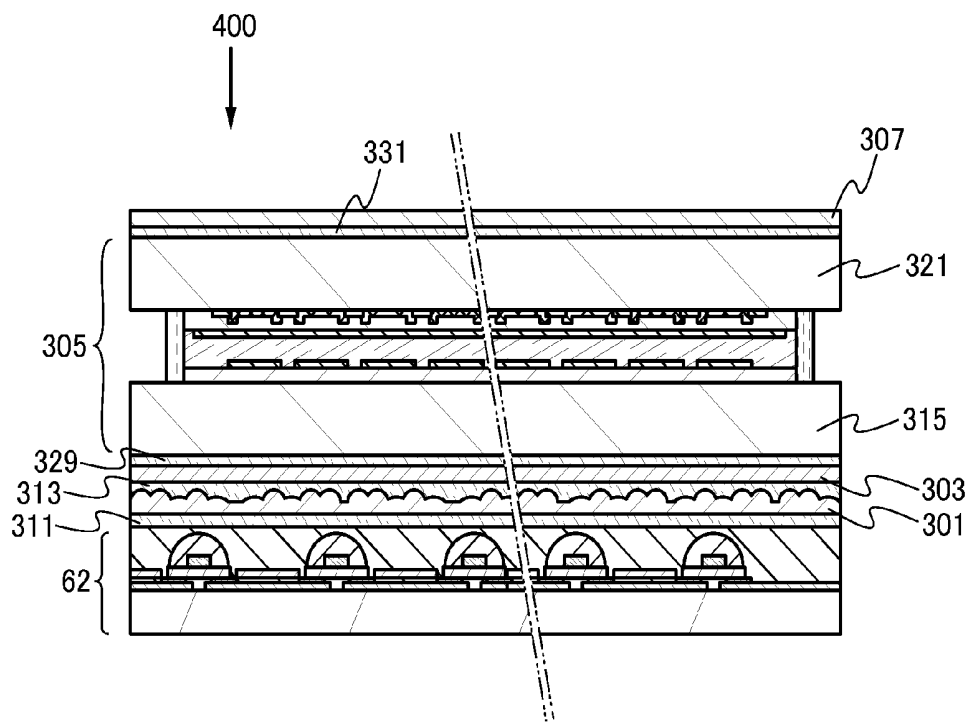


FIG. 9A

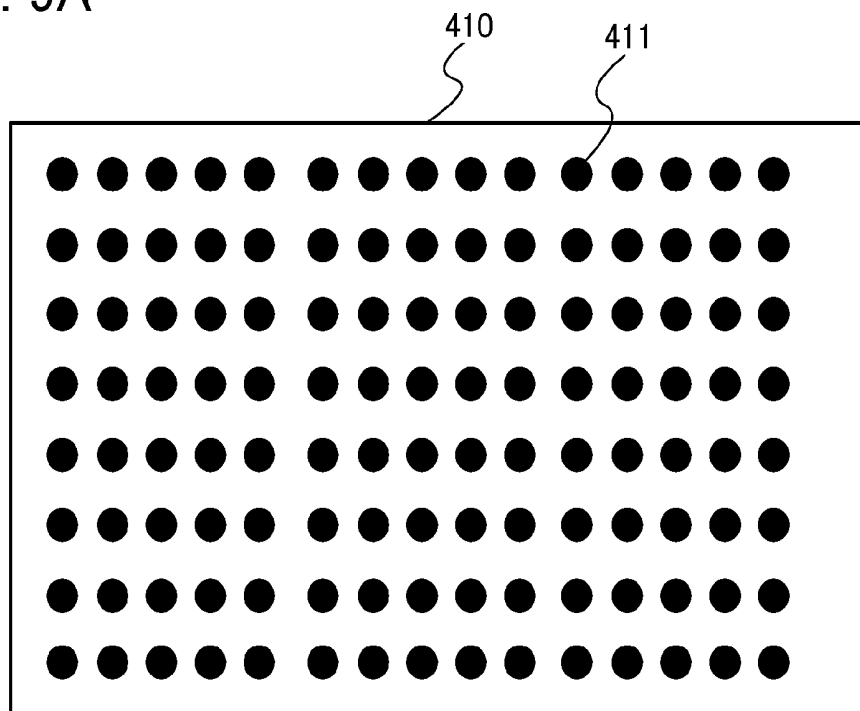


FIG. 9B

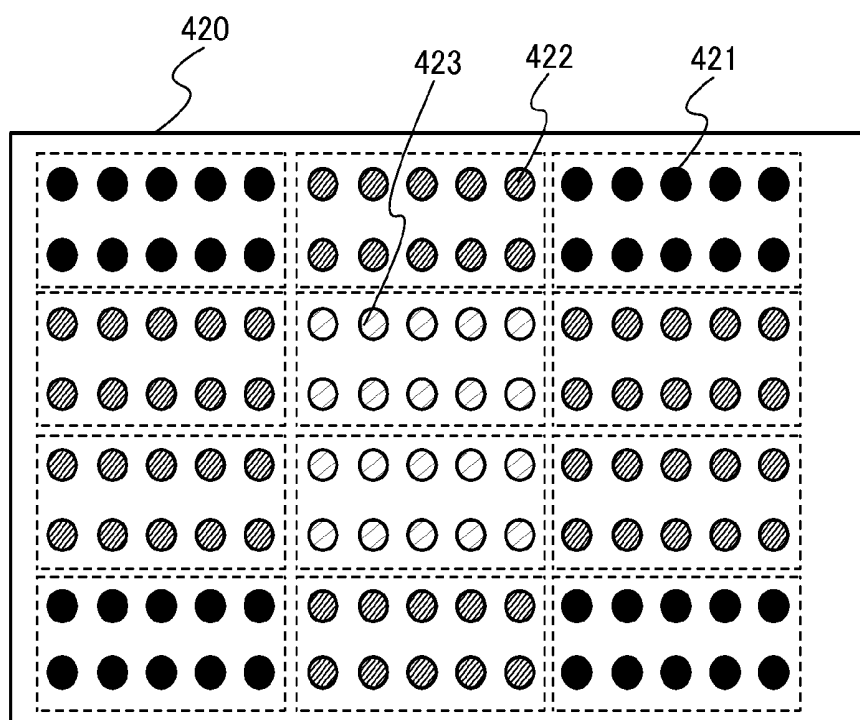


FIG. 10A

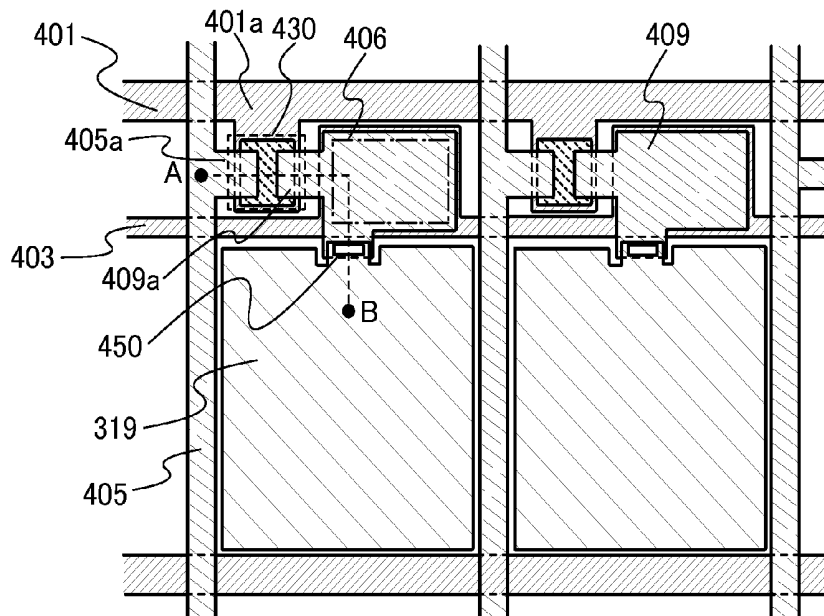


FIG. 10B

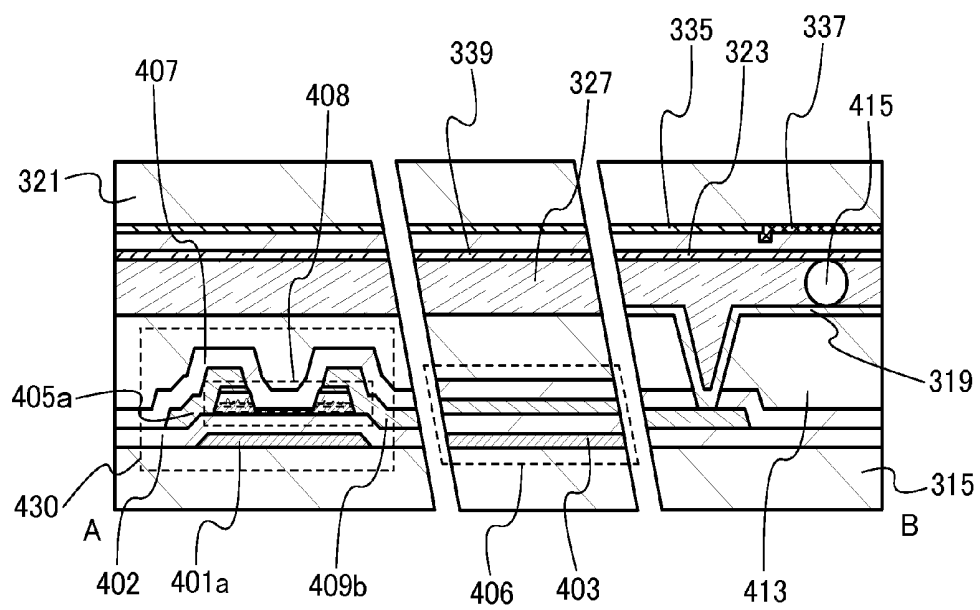


FIG. 11A

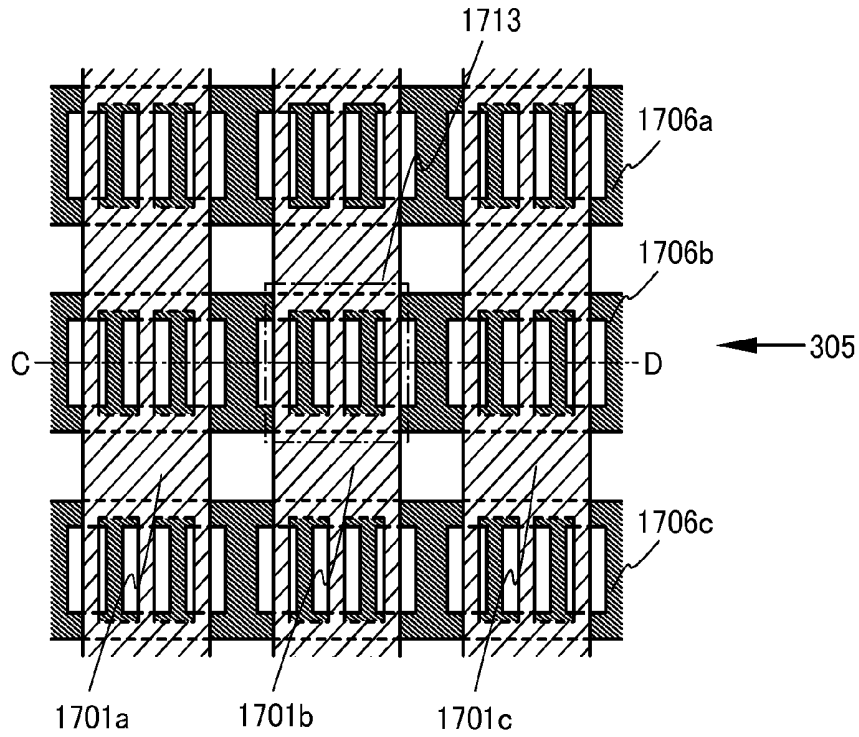


FIG. 11B

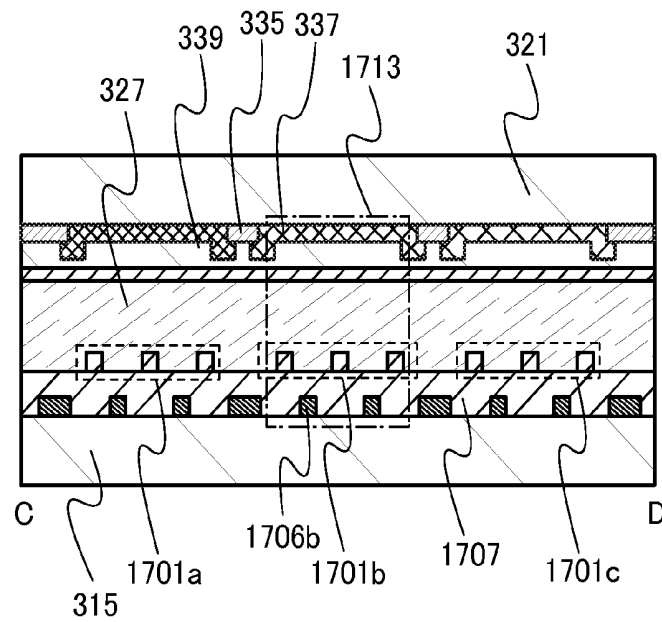


FIG. 12

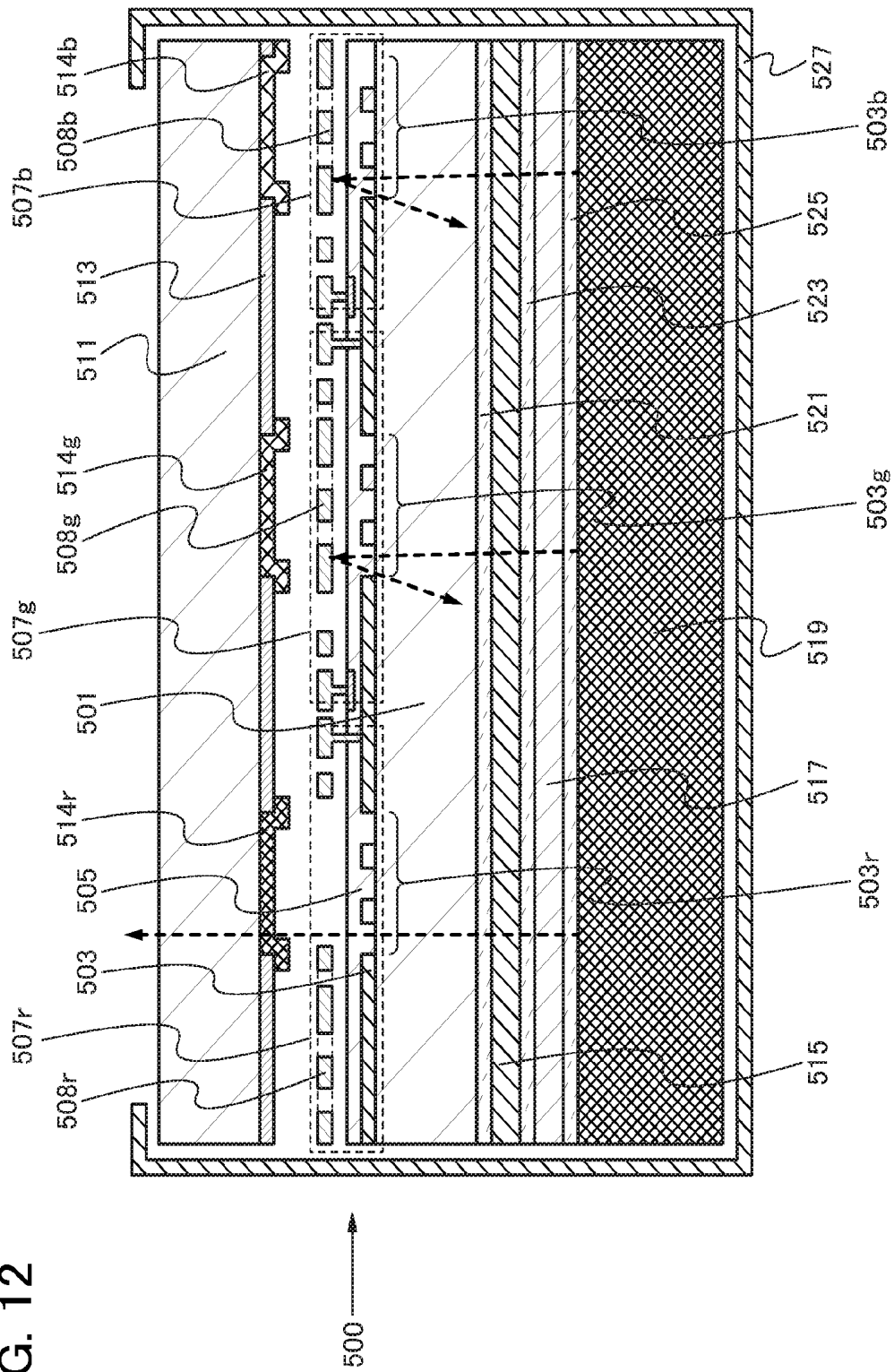


FIG. 13

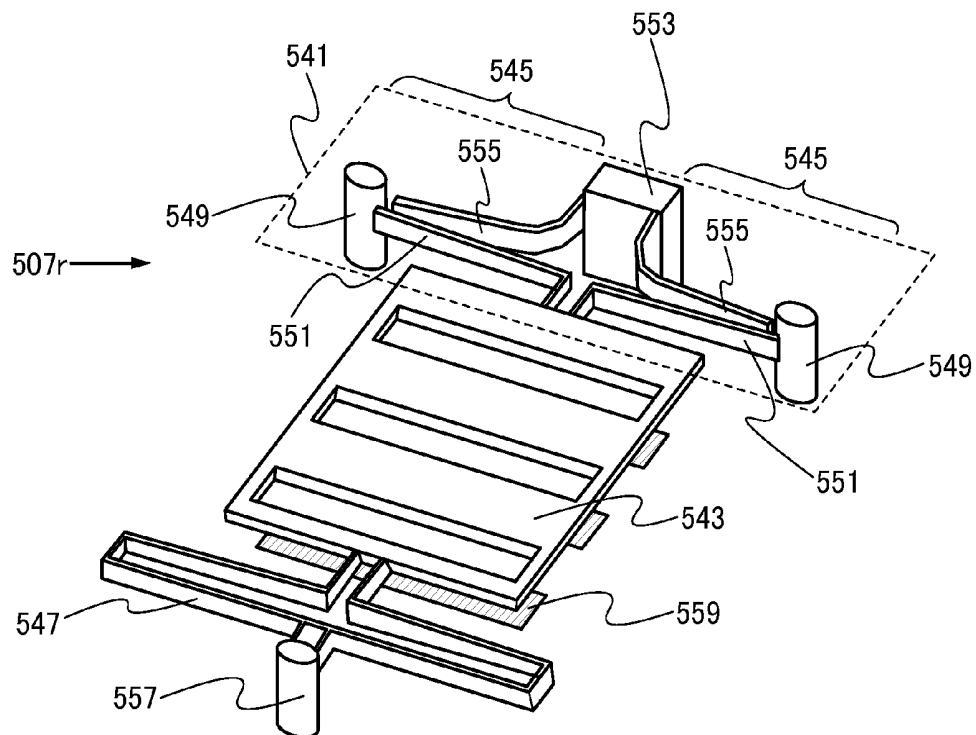


FIG. 14

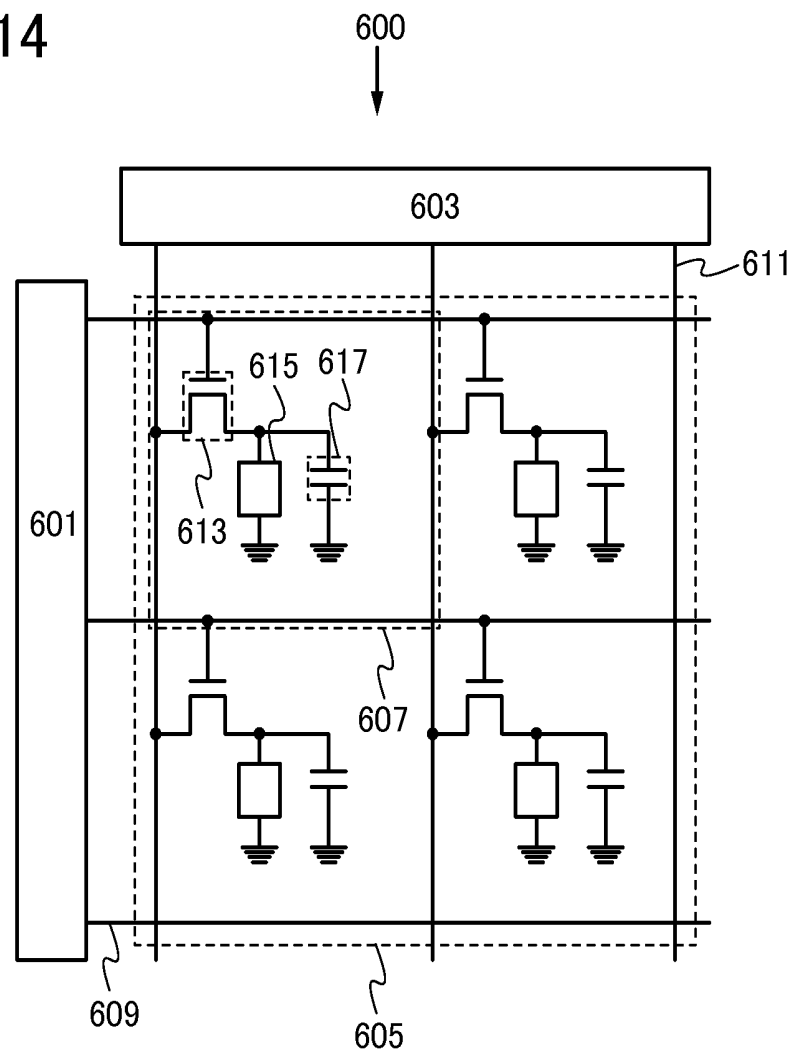


FIG. 15A

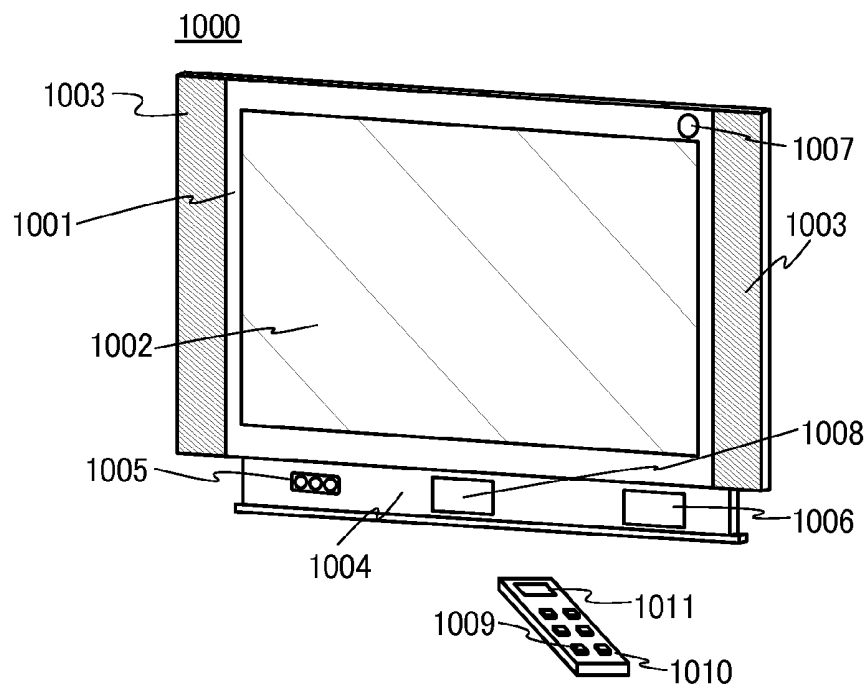
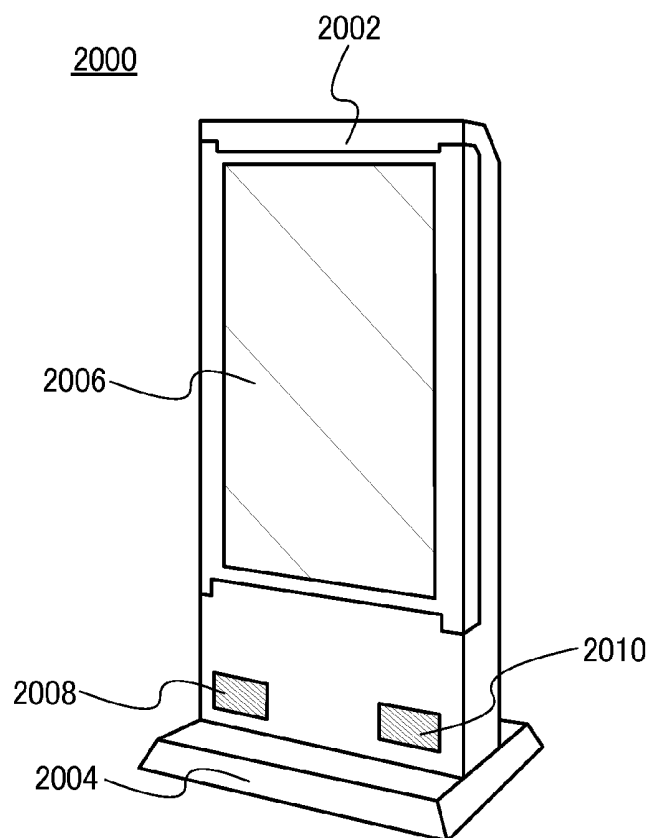


FIG. 15B



LIGHT-EMITTING ELEMENT UNIT AND DISPLAY DEVICE

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a light-emitting element unit, a backlight including a plurality of the light-emitting element units, and a display device including the backlight.

2. Description of the Related Art

As a backlight of a liquid crystal display device, a cold cathode fluorescent lamp has been used. However, in recent years, a light-emitting diode (LED) unit with less power consumption has come into use instead of the cold cathode fluorescent lamp, because the cold cathode fluorescent lamp requires more power consumption in comparison to the light-emitting diode (see Patent Document 1).

The light-emitting diode which has been recently used has a structure in which a phosphor is provided over an LED chip emitting blue light, the phosphor is excited by the blue light to provide yellow light, and then white light is emitted by mixing the yellow light and the blue light.

Further, there is a backlight which emits white light by mixing light emitted from a red-light-emitting diode, light emitted from a blue-light-emitting diode, and light emitted from a green-light-emitting diode.

REFERENCE

[Patent Document 1] Japanese Published Patent Application No. 2004-240412

SUMMARY OF THE INVENTION

An emission spectrum of light from the light-emitting diode in which a phosphor is provided over an LED chip emitting blue light has high emission intensity at a wavelength of 450 nm exhibiting blue and has a peak at a wavelength of 550 nm exhibiting green. However, the intensity of the peak at the wavelength of 550 nm exhibiting green is lower than that of the peak at the wavelength of 450 nm exhibiting blue. In addition, at a wavelength of 700 nm exhibiting red, there is no peak and the intensity is low.

Thus, when white light emitted from the light-emitting diode in which a phosphor is provided over an LED chip emitting blue light is transmitted through a color filter, the light transmitted through the color filter has low color purity of green light and red light. Therefore, color purity of light emitted from a display device is reduced, which causes a problem of low color reproducibility.

In the case where white light is emitted by using a red-light-emitting diode, a blue-light-emitting diode, and a green-light-emitting diode as backlights, the number of components is increased, and it is a factor contributing to increase in cost.

Thus, an object of one embodiment of the present invention is to provide a light-emitting element unit which enables increase in color purity of light emitted through a color filter, and a backlight in which the light-emitting element unit is incorporated. Further, an object of one embodiment of the present invention is to provide a display device with high color purity and high color reproducibility.

One embodiment of the present invention is a light-emitting element unit including a wiring board, a light-emitting element chip provided over the wiring board, a micro optical resonator provided over the wiring board and at the periphery of the light-emitting element chip, and a phosphor layer covering the light-emitting element chip and the micro optical

resonator. Note that in the light-emitting element unit, an organic resin layer which has a convex shape and a light-transmitting property (hereinafter referred to as a light-transmitting convex organic resin layer) may be provided to cover the phosphor layer.

The micro optical resonator includes, over a substrate, a reflective layer, a layer having semi-transmissive and semi-reflective properties (hereinafter referred to as a semi-transmissive reflective layer), and a light-transmitting layer provided between the reflective layer and the semi-transmissive semi-reflective layer. The reflective layer and the semi-transmissive semi-reflective layer are provided at a distance from one another so that light at a predetermined wavelength is reflected and interferes between the two layers to increase the peak intensity. That is, light emitted from the light-emitting element chip is reflected at the phosphor layer to become white light, and then the white light is reflected and interferes in the micro optical resonator, and thereby is emitted as light at a predetermined wavelength. Thus, the light-emitting element unit according to one embodiment of the present invention can emit white light with increased peak intensity at a predetermined wavelength. When the white light passes through a coloring layer of a color to which the above peak corresponds, light of a color with high color purity is produced.

Further, another embodiment of the present invention is a display device which includes a display panel having a coloring layer, and the above-described light-emitting element unit provided in a backlight module. Examples of the display panel having a coloring layer includes: a liquid crystal panel; and a display panel which includes an opening portion provided over a first substrate, MEMS moving over the opening portion in the lateral direction, and a second substrate provided with a coloring layer in a portion corresponding to the opening portion.

The backlight module including the light-emitting element unit emits white light having a peak of a wavelength corresponding to a color of the coloring layer; thus, light transmitted through the coloring layer in the display panel has high color purity. Therefore, the color reproducibility of the display device can be improved.

According to one embodiment of the present invention, a micro optical resonator is provided at the periphery of an LED chip, whereby a light-emitting element unit which enables an increase in color purity of light transmitted through a color filter, and a backlight can be provided. Furthermore, according to one embodiment of the present invention, a display device with high color purity and high color reproducibility can be provided.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1A and 1B are a cross-sectional view and a top view illustrating a light-emitting element unit according to the present invention.

FIGS. 2A-1, 2A-2, 2B, and 2C illustrate a light-emitting element unit according to the present invention.

FIG. 3 is a perspective view illustrating a backlight module according to the present invention.

FIG. 4 is a cross-sectional view illustrating a backlight module according to the present invention.

FIG. 5 is a cross-sectional view illustrating a backlight module according to the present invention.

FIGS. 6A and 6B are a block diagram and a circuit diagram illustrating a display device according to the present invention.

FIGS. 7A and 7B are cross-sectional views each illustrating a display device according to the present invention.

FIG. 8 is a cross-sectional view illustrating a display device according to the present invention.

FIGS. 9A and 9B are top views each illustrating a backlight module according to the present invention.

FIGS. 10A and 10B are a top view and a cross-sectional view illustrating a display device according to the present invention.

FIGS. 11A and 11B are a top view and a cross-sectional view illustrating a display device according to the present invention.

FIG. 12 is a cross-sectional view illustrating a display device according to the present invention.

FIG. 13 is a perspective view illustrating a MEMS switch of a display device according to the present invention.

FIG. 14 is a circuit diagram illustrating a display device according to the present invention.

FIGS. 15A and 15B illustrate an example of a television device and an example of digital signage, respectively.

DETAILED DESCRIPTION OF THE INVENTION

Hereinafter, embodiments of the present invention will be described with reference to drawings. However, the present invention is not limited to the following description. It is easily understood by those skilled in the art that the mode and detail can be variously changed unless departing from the scope and spirit of the present invention. Therefore, the present invention should not be interpreted as being limited to the description of the embodiments to be given below. Note that reference numerals denoting the same portions are commonly used in different drawings.

Embodiment 1

In this embodiment, an LED unit and a backlight which consume less power will be described with reference to FIGS. 1A and 1B and FIGS. 2A-1, 2A-2, 2B, and 2C.

FIG. 1A is a cross-sectional view of an LED unit 30.

The LED unit 30 includes a light-emitting element chip (hereinafter, referred to as an LED chip 33) provided over a wiring board 31, a phosphor layer 35 provided over the LED chip 33, and a light-transmitting convex organic resin layer 37 provided to cover the wiring board 31 and the phosphor layer 35. An electrode of the LED chip 33 is electrically connected to terminals 41a and 41b provided on side walls of the wiring board 31 through wirings 39a and 39b.

FIG. 1B is a top view of the LED chip 33 illustrated in FIG. 1A from which the light-transmitting convex organic resin layer 37 is excluded. As illustrated in FIG. 1B, there is a feature in that a micro optical resonator 43 is provided around the LED chip 33. The micro optical resonator 43 is an element which can make white light change into colored light at a predetermined wavelength.

For the wiring board 31, a glass epoxy resin substrate, a polyimide substrate, a ceramic substrate, an alumina substrate, an aluminum nitride substrate, or the like is used.

For the LED chip 33, a light-emitting diode which can emit blue light is used. As the typical light-emitting diode which can emit blue light, a diode formed using a nitride(Group III)-based compound semiconductor is used, and examples thereof include a diode including a GaN-based material which is represented by a formula, $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ (x is greater than or equal to 0 and less than or equal to 1, y is greater than or equal to 0 and less than or equal to 1, and "x+y" is greater than or equal to 0 and less than or equal to 1).

Typical examples of the phosphor layer 35 include an organic resin layer having a surface on which a phosphor is printed, an organic resin layer whose surface is coated with a phosphor, and an organic resin layer mixed with a phosphor. As a typical example of a yellow phosphor, YAG (yttrium aluminum garnet)-based phosphor, a silicate-based phosphor, or the like can be given.

Note that an example in which an LED chip which can emit blue light is used as the LED chip 33 and a phosphor layer including a phosphor of yellow which is a complementary color of blue is used as the phosphor layer 35 is described here. Alternatively, an LED chip which can emit green light may be used as the LED chip 33, and a phosphor layer including a phosphor of a complementary color of green (red or magenta) may be used as the phosphor layer 35.

Note that blue light has a maximum peak at a wavelength range of 430 to 490 nm in an emission spectrum. Green light has a maximum peak at a wavelength range of 490 to 550 nm in the emission spectrum. Yellow light has a maximum peak at a wavelength range of 550 to 590 nm in the emission spectrum. Red light has a maximum peak at a wavelength range of 640 to 770 nm in the emission spectrum.

The light-transmitting convex organic resin layer 37 is formed using a light-transmitting organic resin. There is no particular limitation on the kind of organic resin, and typically, an ultraviolet curable resin such as an epoxy resin or a silicone resin, a visible light curable resin, or the like can be used as appropriate. The above light-transmitting organic resin is formed to have a predetermined height, a predetermined width, and a predetermined curvature radius so that light with a desired shape can be emitted. The above light-transmitting organic resin may be formed by a droplet discharge method, a coating method, an imprinting method, or the like. Alternatively, an organic resin may be shaped to be convex in advance, and may be compressed while being heated. The light-transmitting convex organic resin layer 37 has a function of diffusing light emitted from the LED chip 33.

An end portion of the phosphor layer 35 is positioned on an outer side of an end portion of the micro optical resonator 43 and the phosphor layer 35 covers the whole of the micro optical resonator 43, whereby light which is fully reflected between a reflective electrode and a semi-transmissive semi-reflective electrode in the micro optical resonator 43 is reflected or refracted at an interface between the phosphor layer 35 and the light-transmitting convex organic resin layer 37. Thus, light incident on the micro optical resonator 43 can be utilized efficiently.

The wirings 39a and 39b are thin wires formed using gold, an alloy including gold, copper, or an alloy including copper.

The terminals 41a and 41b are conductive layers connected to the electrode of the LED chip 33, which are formed using one element selected from nickel, copper, silver, platinum, or gold or an alloy material including any of the elements at 50% or more. The terminals 41a and 41b and the electrode of the LED chip 33 are connected by a wire bonding method using a thermo-compression bonding method or an ultrasonic bonding method.

The micro optical resonator 43 is described below with reference to FIGS. 2A-1, 2A-2, 2B, and 2C.

FIGS. 2A-1 and 2A-2 are enlarged cross-sectional views of the micro optical resonator 43.

As illustrated in FIG. 2A-1, the micro optical resonator 43 includes a reflective layer 49 provided over a substrate 47, a light-transmitting layer 51 provided over the reflective layer 49, and a semi-transmissive semi-reflective layer 53 provided over the light-transmitting layer 51. Further, a protective layer

55 may be provided over the reflective layer 49, the light-transmitting layer 51, and a surface of the semi-transmissive semi-reflective layer 53.

Alternatively, as illustrated in FIG. 2A-2, the micro optical resonator 43 may include the reflective layer 49 provided over the substrate 47, the light-transmitting layer 51 provided over the reflective layer 49, and a semi-transmissive semi-reflective layer 54 provided over the reflective layer 49 and the light-transmitting layer 51. The semi-transmissive semi-reflective layer 54 is provided on side walls of the light-transmitting layer 51 as illustrated in FIG. 2A-2, whereby light which is fully reflected on an upper side and a lower side of the light-transmitting layer 51 is also fully reflected on the side walls of the light-transmitting layer 51. Thus, light entering the micro optical resonator 43 can be utilized efficiently.

The reflective layer 49 is formed using a metal material with high reflectivity. The reflectivity of the reflective layer 49 is 50% or higher, preferably 80% or higher. As the metal material with high reflectivity, aluminum, silver, molybdenum, tungsten, nickel, chromium, an alloy of any of these elements, an AgPdCu alloy, or the like can be given. Further, the reflective layer 49 may have a dielectric multilayer structure in which two kinds of transmissive insulating layers with different refractive indices are alternately stacked. Here, as the refractive indices of the two kinds of transmissive insulating layers are high, or as the number of the layers is large, the reflection efficiency is high. For example, as a stacked structure of a dielectric multilayer structure, a stacked structure of titanium dioxide and silicon dioxide, a stacked structure of zinc sulfide and magnesium fluoride, a stacked structure of amorphous silicon and silicon nitride, or the like can be employed.

The reflective layer 49 can be formed by a sputtering method, an evaporation method, or the like.

The semi-transmissive semi-reflective layer 53 has reflectivity which is higher than or equal to 30% and lower than or equal to 70%, preferably higher than or equal to 40% and lower than or equal to 60%. The semi-transmissive semi-reflective layer 53 can be formed using silver, aluminum, an aluminum alloy, a magnesium-silver alloy, or the like. In order to achieve the above reflectivity, the thickness of the semi-transmissive semi-reflective layer 53 is greater than or equal to 5 nm and less than or equal to 20 nm, preferably greater than or equal to 7 nm and less than or equal to 15 nm.

The semi-transmissive semi-reflective layer 53 can be formed by a sputtering method, an evaporation method, or the like.

As the light-transmitting layer 51, a light-transmitting insulating layer or a light-transmitting conductive layer can be used. Typical examples of the light-transmitting insulating layer include silicon oxide, silicon oxynitride, alumina, aluminum nitride, and an epoxy resin. Typical examples of the light-transmitting conductive layer include indium oxide including tungsten oxide, indium zinc oxide including tungsten oxide, indium oxide including titanium oxide, indium tin oxide including titanium oxide, indium tin oxide, indium zinc oxide, and indium tin oxide to which silicon oxide is added. Note that the light-transmitting layer 51 may have a stacked structure of a plurality of layers.

A structure of a light-emitting element unit which can make white light change into colored light at a predetermined wavelength is described below with reference to FIG. 2B. FIG. 2B is an enlarged view of the phosphor layer 35 covering the LED chip 33 and the micro optical resonator 43 of FIG. 1A.

When light is repeatedly reflected between the reflective layer 49 and the semi-transmissive semi-reflective layer 53

and interferes, the intensity of light at a predetermined wavelength is increased, and an emission spectrum having a sharp peak is obtained. Such a structure is called a micro optical resonator structure (a microcavity structure). Light emitted from the LED chip 33 is reflected at a specific position of the phosphor layer 35, an interface between the phosphor layer 35 and the light-transmitting convex organic resin layer 37, an interface between the light-transmitting convex organic resin layer 37 and the air, or the like to be white light W. Then, the white light W enters the micro optical resonator 43. The entering light is reflected and interferes between the reflective layer 49 and the semi-transmissive semi-reflective layer 53, and after that, light G at a predetermined wavelength is emitted from the micro optical resonator 43. Thus, from the LED unit 30, white light having a sharp peak at a predetermined wavelength in an emission spectrum is emitted.

In order to increase the intensity of light at the predetermined wavelength, in the micro optical resonator 43, a light path length L between the reflective layer 49 and the semi-transmissive semi-reflective layer 53 may be determined in accordance with the wavelength. The light path length L in this case is described below.

An interference between light (θ) at a wavelength λ passing from the semi-transmissive semi-reflective layer 53 to the reflective layer 49 and light returned from the reflective layer 49 to the semi-transmissive semi-reflective layer 53 is represented by Formula 1.

$$\sin(\theta) + \sin(\theta + 2\pi \times 2nL/\lambda + \pi) \quad (\text{Formula 1})$$

By modifying Formula 1, Formula 2 can be obtained.

$$-2 \cos(\theta + 2\pi nL/2) \times \sin(2\pi nL/\lambda) \quad (\text{Formula 2})$$

Formula 2 has the maximum value when the value “ $\sin(2\pi nL/\lambda)$ ” satisfies Formula 3.

$$2\pi nL/\lambda = \pi(2m+1)/2 \quad (m \text{ is an integer}) \quad (\text{Formula 3})$$

From the above, when the light path length L between the reflective layer 49 and the semi-transmissive semi-reflective layer 53 is obtained from Formula 4, light whose wavelength λ has the increased intensity can be emitted from the micro optical resonator 43.

$$L = (2m+1)\lambda/4n \quad (\text{Formula 4})$$

Note that n represents the refractive index of the light-transmitting layer 51.

Further, in the case where the light-transmitting layer 51 has a stacked structure of a plurality of layers (n layers), assuming that the refractive indices of the layers are $n_1, n_2, \dots, n_n$ and the light path lengths of the layers obtained by Formula 4 are $l_1, l_2, \dots, l_n$, the light path length L is the sum of l_1 to l_n .

FIG. 2C is a schematic diagram of the emission intensity of light emitted from the LED unit. A curve 56 indicates an emission spectrum of light emitted from an LED unit which does not include the micro optical resonator 43. The curve 56 has a steep peak at a wavelength in the vicinity of 450 nm exhibiting blue, but the spectrum intensity in the vicinity of 550 nm exhibiting green and the spectrum intensity in the vicinity of 700 nm exhibiting red are low. Thus, even when the white light passes through a red coloring layer or a green coloring layer, the color purity is low in either case.

A curve 56a indicates an emission spectrum of light emitted from an LED unit including the micro optical resonator 43 which has the light path length L enhancing the intensity of red light. A curve 56b indicates an emission spectrum of an LED unit including the micro optical resonator 43 which has the light path length L enhancing the intensity of green light. A curve 56c indicates an emission spectrum of an LED unit

including the micro optical resonator **43** which has the light path length *L* enhancing the intensity of blue light.

The curve **56r** has a steep peak in the vicinity of 700 nm exhibiting red in addition to a peak in the vicinity of 450 nm exhibiting blue.

The curve **56g** has a steep peak in the vicinity of 550 nm exhibiting green in addition to a peak in the vicinity of 450 nm exhibiting blue.

The curve **56b** has a higher peak than the curve **56** in the vicinity of 450 nm exhibiting blue.

As described above, a micro optical resonator having a light path length which enhances the intensity of light at the predetermined wavelength is provided in the LED unit **30**, whereby the intensity of light at the predetermined wavelength emitted from the LED unit **30** can be increased as compared to that emitted from a conventional LED unit in which the micro optical resonator is not provided. Therefore, when the light passes through a coloring layer which transmits light with the increased intensity of light at the predetermined wavelength, the color purity of the transmitted light is increased as compared to the conventional case. For example, when white light having the high intensity of red light passes through a red coloring layer, the red color purity is increased as compared to the conventional case.

Note that in this embodiment, the LED chip **33** emits blue light. Thus, white light emitted from the LED unit has the sufficiently high peak intensity exhibiting blue, and accordingly, the micro optical resonator which makes the intensity of the light at wavelength exhibiting blue increase is not necessarily provided. Similarly, in the case where the LED chip emits red light or green light, the micro optical resonator which makes the intensity of the light at wavelength exhibiting red or green increase is not necessarily provided.

Next, a backlight module including the LED unit illustrated in FIGS. 1A and 1B and FIGS. 2A-1, 2A-2, 2B, and 2C will be described with reference to FIG. 3, FIG. 4, and FIG. 5.

FIG. 3 is a perspective view of a direct-below-type backlight module **40**. The LED units **30** are arranged over a substrate **58** so as to be connected in series. A reflective sheet **61** is provided around the LED units **30**. Although not illustrated, the LED units **30** are electrically connected to a control circuit board via a connector and a wiring. In this case, the control circuit board is provided on the back side of the backlight module **40**.

Next, details of the backlight module are described with reference to FIG. 4. Here, the LED units surrounded by a dashed line **50** in FIG. 3 are used for description.

Over the substrate **58** provided with a wiring **57**, an LED unit **60r** emitting white light having at least a peak of red wavelength, an LED unit **60g** emitting white light having at least a peak of green wavelength, and an LED unit **60b** emitting white light having at least a peak of blue wavelength are provided. Each of the LED units **60r**, **60g**, and **60b** is connected to the wiring **57** with a conductive paste **59**. The reflective sheet **61** is provided over a portion where the substrate **58** and the wiring **57** are exposed.

There is no particular limitation on a substrate used as the substrate **58** as long as it can withstand heat generation in the manufacturing process or practical use. Typical examples of the substrate **58** includes a glass substrate, a plastic substrate, a glass epoxy resin substrate, a polyimide substrate, a ceramic substrate, an alumina substrate, an aluminum nitride substrate, and a printed board. In the case where a printed board where a wiring is formed in advance by a printing method or the like is prepared for the backlight module **40**, the wiring **57** described later need not be formed by an evaporation method, a sputtering method, a droplet discharge method (such as an

inkjet method, screen printing, or offset printing), a coating method, or the like; thus, manufacturing with high yield can be conducted. Here, a glass epoxy resin substrate is used as the substrate **58**.

The wiring **57** is formed using one element selected from aluminum, nickel, copper, silver, platinum, or gold, or an alloy material including any of the elements at 50% or more. The wiring **57** is formed by an evaporation method, an inkjet method, a printing method, or the like.

The conductive paste **59** is formed using an alloy including plural elements selected from tin, silver, bismuth, copper, indium, nickel, antimony, zinc, and the like.

In this embodiment, the LED units **60r**, **60g**, and **60b** are mounted over the substrate **58** by a reflow process using the conductive paste. Typically, a surface of the wiring **57** formed over the substrate **58** is coated with a conductive paste by screen printing or a dispenser method, and the LED units **60r**, **60g**, and **60b** are mounted thereover with a mounter. Then, the conductive paste is heated at 250° C. to 350° C. to be melted, so that terminals of the LED units **60r**, **60g**, and **60b** and the wiring **57** are electrically and mechanically connected.

Instead of the mounting method by a reflow process using a conductive paste, local pressure bonding may be performed with use of an anisotropic conductive adhesive, so that the LED units **60r**, **60g**, and **60b** may be mounted over the substrate **58**.

As the reflective sheet **61**, a substrate provided with white pigment which is light reflective coating is used. Typical examples of the reflective sheet **61** include plastic with a surface on which a white coating is printed or applied, and plastic mixed with the white coating. The white coating includes organic pigment or inorganic pigment such as zinc oxide, titanium oxide, calcium carbonate, silicon oxide, or boron nitride. As the plastic, PET, polyester, polyolefin, or the like can be given. Further, foamable PET including a phosphor material can be used. Alternatively, instead of using the reflective sheet **61**, the substrate **58** and the wiring **57** may be coated with a white solder resist. With the reflective sheet **61** or the white solder resist, light emitted from the LED chip to the substrate side can be reflected.

As the LED units **60r**, **60g**, and **60b**, LED units which are similar to the LED unit **30** illustrated in FIG. 1A can be used.

The LED units **60r**, **60g**, and **60b** include micro optical resonators **43r**, **43g**, and **43b**, respectively. The micro optical resonators **43r**, **43g**, and **43b** emit light of high intensity with respect to red, light of high intensity with respect to green, and light of high intensity with respect to blue by causing interference of light emitted from the LED chips. Light path lengths of the micro optical resonators **43r**, **43g**, and **43b** are determined so as to increase the intensities of light at wavelengths exhibiting red, green, and blue respectively. This is not limited to these three specific colors, the light path lengths of the micro optical resonators **43r**, **43g**, and **43b** can be determined to increase the intensities of light at any wavelength. Thus, the thicknesses of the micro optical resonators **43r**, **43g**, and **43b** are different from each other.

Furthermore, as illustrated in FIG. 5, an organic resin layer **63** having a light-transmitting property (a light-transmitting organic resin layer **63**) may be provided over the LED units **60r**, **60g**, and **60b** and the reflective sheet **61**. For the organic resin layer **63**, any of the organic resin that can be used for the light-transmitting convex organic resin layer **37** can be used as appropriate. Note that the light-transmitting organic resin layer **63** is formed so as not to contain air at an interface between the light-transmitting convex organic resin layer **37** and the light-transmitting organic resin layer **63**. Further, it is preferable to select a material so that the light-transmitting

organic resin layer **63** can have an optical refractive index which uniform luminance of light emitted from the light-transmitting convex organic resin layer **37** and which is close to an optical refractive index of the light-transmitting convex organic resin layer **37**. The light-transmitting organic resin layer **63** is formed by a droplet discharge method, a coating method, a spin coating method, a dipping method, or the like, or may be formed with a tool such as a doctor knife, a roll coater, a curtain coater, or a knife coater.

With use of the above-described LED unit and backlight module, the color purity of light transmitted through the coloring layer can be increased.

Embodiment 2

In this embodiment, a liquid crystal display device including the backlight module described in Embodiment 1 will be described.

The liquid crystal display device in this embodiment can be implemented for both passive matrix type and active matrix type. FIG. 6A is a block diagram illustrating a structure of an active-matrix liquid crystal display device **200**.

In FIG. 6A, the liquid crystal display device **200** includes a pixel portion **210** which displays an image, a signal line driver circuit **214**, a scan line driver circuit **211**, a backlight module **40** which emits light to the pixel portion **210**, and an LED control circuit **212** which controls a signal sent to an LED unit included in the backlight module **40**. In addition, a circuit which is necessary for operating the liquid crystal display device, such as an image processing circuit (an image engine or the like) is included. All of them are provided for the control circuit board described in Embodiment 1. Note that the driver circuits, the processing circuit, and the image processing circuit are each roughly divided into a logical circuit portion and a switch portion or a buffer portion, and details of the structures of the circuits are omitted. Further, part of or entire of the above circuit may be mounted using a semiconductor device such as an IC.

The pixel portion **210** includes a plurality of pixels **215** provided on a liquid crystal panel. The scan line driver circuit **211** is a circuit which drives the pixels **215** and has a function of outputting a plurality of display selection signals which are pulse signals. The signal line driver circuit **214** has a function of generating a display data signal on the basis of an inputted image signal and outputting the generated display data signal. Further, the outputted display data signal is inputted to the corresponding pixel.

FIG. 6B is a circuit diagram of the pixel **215**. In the pixel **215**, a transistor (mainly, a thin film transistor: TFT) is provided as a switching element for controlling potential of a pixel electrode. The pixel **215** includes: a thin film transistor **221** in which a gate is electrically connected to a scan line **219** and a first electrode is electrically connected to a signal line **217**; a capacitor **223** in which a first electrode is electrically connected to a second electrode of the thin film transistor **221** and a second electrode is electrically connected to a wiring for supplying a fixed potential (also referred to as a capacitor line); and a liquid crystal element **225** in which one of electrodes (also referred to as a pixel electrode) is electrically connected to the second electrode of the thin film transistor **221** and the first electrode of the capacitor **223** and the other electrode (also referred to as a counter electrode) is electrically connected to a wiring for supplying a counter potential.

In this specification, a liquid crystal panel displays an image by controlling light transmission or non-transmission by the optical modulation action of a liquid crystal. The optical modulation action of a liquid crystal is controlled by

an electric field applied to the liquid crystal (including a horizontal electric field, a vertical electric field, and an oblique electric field).

Next, an embodiment of the liquid crystal display device **200** is described with reference to a cross-sectional view of the liquid crystal display device **200** illustrated in FIGS. 7A and 7B. The liquid crystal display device illustrated in FIG. 7A includes: the backlight module **40** described in Embodiment 1; a diffusion plate **301** overlapping with the backlight module **40**; a first polarizing plate **303** overlapping with the backlight module **40** and the diffusion plate **301**; a liquid crystal panel **305** overlapping with the backlight module **40**, the diffusion plate **301**, and the first polarizing plate **303**; and a second polarizing plate **307** overlapping with the backlight module **40**, the diffusion plate **301**, the first polarizing plate **303**, and the liquid crystal panel **305**. Note that although not illustrated, a reflective plate may be provided on an outer side of the backlight module **40**, so that light leaking through the backlight module **40** is reflected and incident on the liquid crystal panel **305**.

A circuit necessary for operating the liquid crystal display device **200** is connected to the liquid crystal panel **305** and the backlight module **40**. Note that the scan line driver circuit **211** and the signal line driver circuit **214** may be provided in the liquid crystal panel **305**.

Next, details of components included in the liquid crystal display device **200** are described.

As the backlight module **40**, the backlight module described in Embodiment 1 is used. The backlight module described in Embodiment 1 includes the micro optical resonator having a light path length which enhances the intensity of light at the predetermined wavelength; thus, light emitted from the LED unit can have higher intensity of light at the predetermined wavelength than white light emitted from the conventional LED unit. Therefore, when the light passes through a coloring layer which transmits a color of high intensity at the predetermined wavelength, the color purity of the transmitted light is increased more than the convention case. As a result, color reproducibility of the display device in this embodiment can be increased.

There is no particular limitation on the first polarizing plate **303** which polarizes light emitted from the diffusion plate **301** as long as it can make the light emitted from the diffusion plate **301** polarize. A commercial product may be used, and one which is conventionally used can be employed. For example, a polarizing plate including a high molecule such as polyvinyl alcohol can be used. The first polarizing plate **303** may have a plate shape or a sheet shape (a film shape). In addition, it is preferable to use a polarizing plate which has the optical refractive index as equivalent as possible to that of another component included in the liquid crystal display device **200**.

The liquid crystal panel **305** includes a layer including a switching element (hereinafter, referred to as an element layer **317**) over a substrate **315**, a pixel electrode **319** formed over the element layer **317**, a counter substrate **321** provided with a light-blocking layer **335**, a coloring layer **337**, a protective layer **339**, and a common electrode **323**, a sealant **325**, and a liquid crystal **327** which transmits or blocks incident light. Although not illustrated in FIGS. 7A and 7B, a spacer is provided so that a distance (a cell gap) between the pixel electrode **319** and the common electrode **323** is controlled to be constant. As the spacer, a bead spacer or a spacer obtained by selective etching of an insulating layer (a post spacer) can be used.

As the substrate **315** and the counter substrate **321**, a light-transmitting substrate is preferable, for example, a glass sub-

strate of barium borosilicate glass, aluminoborosilicate glass, or the like; a quartz substrate; or a plastic substrate which can withstand a process temperature in a manufacturing process of the liquid crystal display device **200** and the element layer **317** can be used. Further, as the substrate **315** and the counter substrate **321**, a glass substrate having any of the following sizes can be used: the 3rd generation (550 mm×650 mm), the 3.5th generation (600 mm×720 mm or 620 mm×750 mm), the 4th generation (680 mm×880 mm or 730 mm×920 mm), the 5th generation (1100 mm×1300 mm), the 6th generation (1500 mm×1850 mm), the 7th generation (1870 mm×2200 mm), the 8th generation (2200 mm×2400 mm), the 9th generation (2400 mm×2800 mm or 2450 mm×3050 mm), and the 10th generation (2950 mm×3400 mm).

A typical example of the switching element formed in the element layer **317** includes a transistor. Although a transistor is described later, the transistor preferably uses a semiconductor, in a channel, which has characteristics needed for operation of a liquid crystal display device in a variety of conditions (e.g., temperature characteristics which allows the device to operate under high temperature and low temperature). Amorphous silicon can be used for a channel region, but as a typical example of a semiconductor with more improved temperature characteristics, microcrystalline silicon having a plurality of crystalline regions, polysilicon, or the like is preferably used. Further, an oxide semiconductor can be used for a channel region, and an In—Ga—Zn—O-based oxide or the like is given as an oxide semiconductor. A transistor including the above-described semiconductor has a small shift in the threshold voltage and high reliability even when the temperature of the transistor becomes increased by heat generation of the backlight module **40** or heat from external light; thus, the transistor operates with high performance even under an environment where the temperature largely changes.

The pixel electrode **319** and the common pixel electrode **323** can be formed using a light-transmitting conductive material such as indium oxide containing tungsten oxide, indium zinc oxide containing tungsten oxide, indium oxide containing titanium oxide, indium tin oxide containing titanium oxide, indium tin oxide, indium zinc oxide, or indium tin oxide containing silicon oxide.

The light-blocking layer **335** is formed using a light-blocking material that reflects or absorbs light. The light-blocking layer can be formed using, for example, a black organic resin and may be formed by mixing a black resin of a pigment material, carbon black, titanium black, or the like into a resin material such as photosensitive or non-photosensitive polyimide. Alternatively, a light-blocking metal layer can be used, which is made of chromium, molybdenum, nickel, titanium, cobalt, copper, tungsten, or aluminum, for example.

The coloring layer **337** can be formed using a light-transmitting chromatic-color resin layer. As the light-transmitting chromatic-color resin layer, a photosensitive or non-photosensitive organic resin can be given as a typical example. Use of the photosensitive organic resin layer makes it possible to reduce the number of resist masks; thus, the steps are simplified, which is preferable.

Chromatic colors are colors except achromatic colors such as black, gray, or white. The coloring layer is formed of a material which only transmits light colored chromatic color in order to function as the color filter. As chromatic color, red, green, blue, or the like can be used. Alternatively, cyan, magenta, yellow, or the like may also be used. "Transmitting only the chromatic color light" means that light transmitted through the coloring layer has a peak at the wavelength of the chromatic color light.

An optimal thickness of the coloring layer **337** may be adjusted as appropriate in consideration of relation between the concentration of a coloring material included and the transmissivity of light.

The protective layer **339** is formed of a flat insulating layer. As a typical example of the protective layer **339**, an acrylic resin, an epoxy resin, or the like can be used.

Note that the coloring layer **337** is provided on the counter substrate **321**, but a coloring layer may be formed to function as an interlayer insulating layer included in the element layer **317**. For example, a light-transmitting chromatic-color resin layer functioning as a color filter layer may be used for an interlayer insulating layer.

In the case where the interlayer insulating layer is formed directly on the element substrate side as a coloring layer, the problem of misalignment between the coloring layer and a pixel region does not occur, whereby the formation region can be controlled more precisely even when a pixel has a minute pattern. In addition, the same insulating layer serves as the interlayer insulating layer and the coloring layer, which brings advantages of process simplification and cost reduction.

The optical modulation action of the liquid crystal **327** is controlled by an electric field (including a horizontal electric field, a vertical electric field, and a diagonal electric field) applied to the liquid crystal **327**. Note that the following can be used for the liquid crystal **327** and a driving mode of the liquid crystal element: a nematic liquid crystal, a cholesteric liquid crystal, a smectic liquid crystal, a discotic liquid crystal, a thermotropic liquid crystal, a lyotropic liquid crystal, a low-molecular liquid crystal, a high-molecular liquid crystal, a ferroelectric liquid crystal, an anti-ferroelectric liquid crystal, a main chain type liquid crystal, a side chain type high-molecular liquid crystal, a plasma address liquid crystal (PALC), a banana-shaped liquid crystal, a TN (Twisted Nematic) mode, an STN (Super Twisted Nematic) mode, an IPS (In-Plane-Switching) mode, an FFS (Fringe Field Switching) mode, an MVA (Multi-domain Vertical Alignment) mode, a PVA (Patterned Vertical Alignment), an ASV (Advanced Super View) mode, an ASM (Axially Symmetric aligned Micro-cell) mode, an OCB (Optical Compensated Birefringence) mode, an ECB (Electrically Controlled Birefringence) mode, an FLC (Ferroelectric Liquid Crystal) mode, an AFLC (Anti Ferroelectric Liquid Crystal) mode, a PDLC (Polymer Dispersed Liquid Crystal) mode, and a guest host mode. Note that this invention is not limited thereto, and various kinds of liquid crystal elements can be used. The alignment of the liquid crystal **327** can be easily performed by rubbing treatment with use of an alignment film.

Alternatively, a blue-phase liquid crystal for which an alignment film is not necessary may be used for the liquid crystal **327**. A blue phase is one of liquid crystal phases, which is generated just before a cholesteric phase changes into an isotropic phase while temperature of cholesteric liquid crystal is increased. Since the blue phase is generated within an only narrow range of temperature, liquid crystal composition containing a chiral agent so as to improve the temperature range is used for the liquid crystal layer. As for the liquid crystal composition which contains a blue-phase liquid crystal and a chiral material, the response speed is as high as 10 μs to 100 μs, alignment treatment is not necessary and viewing angle dependence is low due to optical isotropy.

The sealant **325** has a function of sealing the liquid crystal **327** between the substrate **315** and the counter substrate **321**.

The sealant **325** is preferably a visible-light curing resin, an ultraviolet curing resin, or a thermosetting resin. Typically, an acrylic resin, an epoxy resin, an amine resin, or the like can be

used. Further, a photopolymerization initiator (typically, an ultraviolet light polymerization initiator), a thermosetting agent, a filler, or a coupling agent may be included in the sealant.

There is no particular limitation on the second polarizing plate **307** as long as it can make light emitted from the liquid crystal panel **305** polarize. The same plate as the first polarizing plate **303** can be used. In addition, it is preferable to use a polarizing plate which has the optical refractive index as equivalent as possible to that of another component included in the liquid crystal display device **200**. The second polarizing plate **307** is provided so that a slit thereof is perpendicular to a slit of the first polarizing plate **303**. The second polarizing plate **307** may have a plate shape or a sheet shape (a film-like shape).

In this manner, the liquid crystal display device **200** can be manufactured.

Next, as another embodiment of the liquid crystal display device **200**, a liquid crystal display device **300** in which an optical member is provided between the diffusion plate **301** and the first polarizing plate **303** is described. The optical member improves front luminance of light emitted from the backlight module **40** and having uniform brightness at the diffusion plate **301**.

FIG. 7B is a cross-sectional view of the liquid crystal display device **300**. As an optical member **333** improving frontal luminance of a pixel portion in the liquid crystal display device, a luminance improving sheet (film) such as a prism sheet or a microlens sheet can be used, which is an optical member that makes light enter the liquid crystal panel **305** as vertically as possible.

The backlight module **40** and the diffusion plate **301** described in the liquid crystal display device **200** of FIG. 7A can be used here as appropriate. The number of luminance improving sheets (films) to be used may be one, but when a plurality of luminance improving sheets (films) are used, frontal luminance of the pixel portion in the liquid crystal display device can be improved. In such a case, the luminance improving sheets (films) may be just arranged so that air is held between the sheets.

Further, as the first polarizing plate **303**, the liquid crystal panel **305**, and the second polarizing plate **307**, those described in the liquid crystal display device **200** can be used as appropriate.

The liquid crystal panel **305** described in the liquid crystal display device **200** is provided to overlap with the backlight module **40** to which the diffusion plate **301** and the optical member **333** are bonded, whereby the liquid crystal display device **300** can be manufactured.

Next, a liquid crystal display device which can uniform brightness of light emitted from the backlight module described in the liquid crystal display devices **200** and **300** is described with reference to FIG. 8.

A liquid crystal display device **400** illustrated in FIG. 8 includes a backlight module **62** which is planarized and has the light-transmitting organic resin layer **63** as illustrated in FIG. 5. Further, the backlight module **62**, the diffusion plate **301**, the first polarizing plate **303**, the liquid crystal panel **305**, and the second polarizing plate **307** are bonded to one another with light-transmitting adhesives **311**, **313**, **329**, and **331**.

That is, in the liquid crystal display device **400**, the backlight module **62**, the diffusion plate **301**, the first polarizing plate **303**, the liquid crystal panel **305**, and the second polarizing plate **307** overlap with and are bonded to one another and sealed. The liquid crystal display device **400** in which all components are bonded is not provided with a layer containing air and having smaller refractive index than the diffusion

plate **301**, the first polarizing plate **303**, the liquid crystal panel **305**, and the second polarizing plate **307**. In the liquid crystal display device **400**, differences of optical refractive indices among the above components are small, and light reflection in the liquid crystal display device **400** is suppressed, so that light emitted from the backlight module **62** can be efficiently utilized. As a result, power consumption of the LED unit and display power of the display device can be reduced.

As the light-transmitting adhesives **311**, **313**, **329**, and **331**, it is preferable to use an adhesive which has an optical refractive index as equivalent as possible to that of the backlight module **62** and the diffusion plate **301**. For example, as the light-transmitting adhesives **311**, **313**, **329**, and **331**, an adhesive containing an epoxy resin, an adhesive containing a urethane resin, an adhesive containing a silicone resin, or the like can be used. The adhesives are formed, depending on a selected material, by a droplet discharge method, a coating method, a spin coating method, a dipping method, or the like. Further, the adhesives may be formed with a tool such as a doctor knife, a roll coater, a curtain coater, or a knife coater.

Next, a driving method of an LED unit in the liquid crystal display device which is one embodiment of the present invention is described.

FIGS. 9A and 9B are top views of backlight modules. In the case where an image is displayed by lighting LED units **411** constantly in a backlight module **410** and controlling light transmission or non-transmission with liquid crystals in the liquid crystal panel, a complicated light-emitting element control circuit is not needed, which is a simplified structure (see FIG. 9A).

However, consumed power of the LED unit accounts for a large share of power consumed by the entire liquid crystal display device. That is, it is not preferable in terms of power consumption that the LED units are constantly lit.

As an effective driving method of an LED unit in a direct-below type backlight module which is one embodiment of the present invention, there is a local dimming method in which LED units are divided into a plurality of regions and the LED units themselves have contrast between the regions in accordance with contrast of a displayed image.

A backlight module **420** illustrated in FIG. 9B is in a local dimming state. Luminance of LED units **421** and **422** in regions corresponding to dark image portions is decreased, and luminance of LED units **423** in a region corresponding to a bright image portion is increased. By driving the LED units in this way, the contrast ratio of an image is increased, and power consumption of the LED units can be reduced.

Here, details of the liquid crystal panel **305** are described. First, an active-matrix liquid crystal panel is described with reference to FIGS. 10A and 10B.

FIG. 10A is a top view of the liquid crystal panel **305**, which illustrates two pixels.

In FIG. 10A, a plurality of signal lines **405** (including a source electrode **405a**) are arranged in parallel (is extended in the vertical direction in the drawing) to be spaced from each other. A plurality of scan lines **401** (including a gate electrode **401a**) are provided apart from each other and extended in a direction generally perpendicular to the signal lines **405** (a horizontal direction in the drawing). The plurality of signal lines are connected to the signal line driver circuit **214** (see FIG. 6A), and the plurality of scan lines and capacitor wirings **403** are connected to the scan line driver circuit **211** (see FIG. 6A).

In addition, the capacitor wirings **403** are adjacent to the plurality of scan lines **401** and extended in a direction parallel to the scan lines **401**, that is, in a direction generally perpen-

dicular to the signal lines **405** (in the horizontal direction in the drawing). A storage capacitor **406** is surrounded by a dashed-dotted line in FIG. **10A**, and includes a gate insulating layer **402** serving as a dielectric, the capacitor wiring **403**, and a drain wiring **409** (including a drain electrode **409a**). A pixel electrode **319** is electrically connected to the drain wiring **409** through an opening portion **450**.

A transistor **430** which controls the potential of the pixel electrode **319** is provided at an upper left corner of the drawing. A plurality of pixel electrodes **319** and a plurality of transistors **430** are arranged in matrix.

Further, a pixel structure is not limited to that illustrated in FIGS. **10A** and **10B**, and a capacitor may be formed without providing a capacitor wiring. In such a structure, the pixel electrode overlaps with a scan line of an adjacent pixel with a gate insulating layer and another insulating layer interposed therebetween. In this case, the capacitor wiring can be omitted, whereby the aperture ratio of a pixel can be increased.

FIG. **10B** is a cross-sectional view taken along line A-B in FIG. **10A**. Divided portions in FIG. **10B** correspond to omitted portions between the line A-B in FIG. **10A**.

Hereinafter, a structure of the transistor **430** is described. The transistor **430** is an inverted-staggered thin film transistor (TFT) which includes, over the substrate **315** having an insulating surface, a gate electrode **401a**, the gate insulating layer **402**, a semiconductor layer **408**, the source electrode **405a**, and the drain electrode **409a**. The above components can be formed through the desired deposition steps, the desired photolithography steps, and the desired etching steps.

There is no particular limitation on a structure of a transistor which can be applied to the liquid crystal panel **305**. For example, a staggered type or planar type transistor having a top-gate structure or bottom-gate structure can be used. The transistor may have a single-gate structure in which one channel formation region is formed, a double-gate structure in which two channel formation regions are formed, or a triple-gate structure in which three channel formation regions are formed. Alternatively, the transistor may have a dual-gate structure having two gate electrodes, one of which is provided above a channel region with a gate insulating layer interposed therebetween and the other of which is provided below the channel formation region with another gate insulating layer interposed therebetween. The transistor of this embodiment has a single-gate structure.

An insulating layer **407** is provided to cover the transistor **430** and to be in contact with the semiconductor layer **408**, and an interlayer insulating layer **413** is stacked thereover.

For the semiconductor layer **408**, as described above, it is preferable to use a semiconductor having characteristics needed for operation of the liquid crystal display device even in a variety of conditions (e.g., temperature characteristics which allows the device to operate under high temperature and low temperature). As a typical example of the semiconductor having temperature characteristics, although amorphous silicon can be used, microcrystalline silicon which has a plurality of crystalline regions, or polycrystalline silicon is preferable in order to obtain more excellent temperature characteristics. Alternatively, an oxide semiconductor can be used. Examples of an oxide semiconductor include In—Ga—Zn—O-based oxide and the like. Further, a transistor element including the above-described semiconductor has a small shift in the threshold voltage and high reliability, even when the temperature of the transistor element is increased by heat generation of the backlight module or heat from external light; thus, the transistor element operates with high performance even under an environment where the temperature largely changes.

In the capacitor **406** indicated by a dashed line, the gate insulating layer **402** serving as a dielectric is stacked between the capacitor wiring **403** and the drain electrode **409a** as described above. The capacitor wiring **403** is formed from the same layer as the gate electrode **401a** under the same condition; thus, it is formed at the time of formation of the gate electrode **401a**. Therefore, there is no need for forming the capacitor **406** independently from the transistor **430**. The capacitor **406** can be formed by a desired photolithography step through a procedure for forming the transistor **430**.

The substrate **315** and the counter substrate **321** are bonded to be fixed with the sealant **325** so that the liquid crystal **327** is interposed therebetween (see FIGS. **7A** and **7B**). The above-described materials can be used for the sealant **325** and the liquid crystal **327**. The liquid crystal **327** can be formed by a dispenser method (a dropping method), or an injection method by which liquid crystal is injected using a capillary phenomenon or the like after the substrate **315** is bonded to the counter substrate **321**. In the case where a photocurable resin such as an ultraviolet curable resin is used as the sealant **325** and a liquid crystal layer is formed by a dropping method, the sealant **325** may be cured by the light irradiation step of the polymer stabilization treatment.

In addition, a spacer **415** is provided so that the distance (the cell gap) between the pixel electrode **319** and the common pixel electrode **323** is controlled to be constant. Although a bead spacer is used here, a spacer obtained by selective etching of an insulating layer (a post spacer) may be used. In the liquid crystal display device including the liquid crystal **327**, the cell gap is preferably greater than or equal to 1 μm and less than or equal to 20 μm . In this specification, the thickness of a cell gap refers to the length (film thickness) of a thickest part of the liquid crystal.

In addition, a light-blocking layer (a black matrix) is provided in a region overlapping with the semiconductor layer and a contact hole of the transistor **430** or between pixels. Further, a coloring layer is provided in a region corresponding to the pixel electrode.

Next, a passive-matrix liquid crystal panel **305** which can be manufactured more easily than the active-matrix liquid crystal panel **305** in which a switching element (a transistor) is provided in the pixel, is described with reference to FIGS. **11A** and **11B**. In the passive-matrix liquid crystal panel **305**, it is not necessary to provide a switching element (a transistor) in a pixel, which enables the passive-matrix liquid crystal panel **305** to be easily manufactured.

FIG. **11A** is a top view of the passive-matrix liquid crystal panel **305**. FIG. **11B** is a cross-sectional view taken along line C-D in FIG. **11A**. The liquid crystal **327**, the light-blocking layer **335**, the coloring layer **337**, the protective layer **339**, and the counter substrate **321** are provided as illustrated in FIG. **11B** though they are not illustrated in FIG. **11A**.

Common electrodes **1706a**, **1706b**, and **1706c**, an insulating layer **1707**, and pixel electrodes **1701a**, **1701b**, and **1701c** are provided between the counter substrate **321** and the substrate **315**. The pixel electrodes **1701a**, **1701b**, and **1701c** correspond to the pixel electrode **319** for active matrix type (see FIGS. **7A** and **7B**), and the common electrodes **1706a**, **1706b**, and **1706c** correspond to the common electrode **323** for active matrix type (see FIGS. **7A** and **7B**). Further, the pixel electrodes **1701a**, **1701b**, and **1701c** are controlled by a common driver corresponding to a scan line driver circuit for active matrix type, and the common electrodes **1706a**, **1706b**, and **1706c** are controlled by a segment driver corresponding to a signal line driver circuit for active matrix type.

The pixel electrodes **1701a**, **1701b**, and **1701c** and the common electrodes **1706a**, **1706b**, and **1706c** each have a

shape with an opening pattern which includes a rectangular opening (slit) in a pixel region of a liquid crystal element.

With an electric field formed between the pixel electrodes **1701a**, **1701b**, and **1701c** and the common electrodes **1706a**, **1706b**, and **1706c**, the liquid crystal **327** is controlled. An electric field in a lateral direction is formed for the liquid crystal, so that liquid crystal molecules can be controlled using the electric field. The liquid crystal molecules can be controlled in the direction parallel to the substrate, whereby a wide viewing angle is obtained.

The counter substrate **321** is provided with the light-blocking layer **335**, the coloring layer **337**, and the protective layer **339**.

Although not illustrated, the spacer can be used for keeping the cell gap, and the above-described sealant can be used for sealing the liquid crystal **327** in the same manner as the liquid crystal display device of the active matrix type.

Note that this embodiment can be implemented in free combination with any of the other embodiments.

Embodiment 3

In this embodiment, a display device which controls the amount of light, in each pixel, transmitted from a backlight with use of micro electro mechanical systems (MEMS) will be described with reference to FIG. 12, FIG. 13, and FIG. 14.

FIG. 12 is a cross-sectional view of a display device **500** which controls the amount of light, in each pixel, transmitted from a backlight with use of MEMS having a three-dimensional structure and a microstructure part of which can be moved.

A reflective layer **503** is formed over a first substrate **501**. A light-transmitting insulating layer **505** is provided over the reflective layer **503**. MEMS switches **507r**, **507g**, and **507b** are formed over the light-transmitting insulating layer **505**. Note that although not illustrated, the light-transmitting insulating layer **505** includes a plurality of insulating layers, and transistors connected to the MEMS switches **507r**, **507g**, and **507b** are formed between the insulating layers. As the transistors, the transistor described in Embodiment 2 can be used as appropriate. On a second substrate **511** facing the first substrate **501**, a light-blocking layer **513** is formed in a portion facing the reflective layer **503**, and coloring layers **514r**, **514g**, and **514b** are formed in portions facing opening portions **503r**, **503g**, and **503b** surrounded by the reflective layer **503**. Note that the coloring layer **514r** transmits red light, the coloring layer **514g** transmits green light, and the coloring layer **514b** transmits blue light.

Further, a diffusion plate **515**, a luminance improvement sheet **517**, and a backlight **519** are provided on the first substrate **501** side in this order. The first substrate **501** and the diffusion plate **515**, the diffusion plate **515** and the luminance improvement sheet **517**, and the luminance improvement sheet **517** and the backlight **519** are bonded with light-transmitting adhesives **521**, **523**, and **525**.

A chassis **527** formed using a metal sheet or molded plastic is provided to be extended from the second substrate **511** side so as to cover the backlight **519**.

In the display device **500** described in this embodiment, for example, the opening portions **503g** and **503b** surrounded by the reflective layer **503** are covered by a non-opening portion in a shutter **508g** of the MEMS switch **507g** and a non-opening portion in a shutter **508b** of the MEMS switch **507b**, whereby light from the backlight **519** is reflected at the non-opening portions in the shutters **508g** and **508b** and is not transmitted. A shutter **508r** of the MEMS switch **507r** does not cover the opening portion **503r** surrounded by the reflec-

tive layer **503** but moves to an upper portion of the reflective layer **503**. Therefore, light from the backlight **519** passes through the opening portion **503r**, and light of a color of a coloring layer (in this case, red) is emitted.

Further, luminance of each pixel or gradation can be controlled with the number of opening and closing times of the MEMS switch **507** or the duty ratio.

As the first substrate **501** and the second substrate **511**, substrates similar to those of the liquid crystal display device described in Embodiment 2 can be used as appropriate.

The reflective layer **503** is formed using aluminum, silver, molybdenum, tungsten, nickel, chromium, an alloy containing any of these, an AgPdCu alloy, or the like. The thickness of the reflective layer **503** is greater than or equal to 30 nm and less than or equal to 1000 nm. The opening portion may have a rectangular shape, a circular shape, an elliptical shape, a polygonal shape, or the like. Through the opening portions **503r**, **503g**, and **503b**, light emitted from the backlight **519** is transmitted to the outside of the display device. Note that light which is emitted from the backlight **519** and does not pass through the opening portion is reflected at the reflective layer **503** and reflected again at a backlight module, so that the reflected light can be reused.

The reflective layer **503** can be formed as follows: a film is formed by a sputtering method, an evaporation method, or the like; and the film is partly etched by a photolithography step. Alternatively, the reflective layer **503** can be formed by a printing method, an inkjet method, or the like.

The light-transmitting insulating layer **505** is formed using silicon oxide, silicon nitride, silicon oxynitride, silicon nitride oxide, or the like by a sputtering method, a CVD method, an evaporation method, or the like.

The MEMS switches **507r**, **507g**, and **507b** have the same structure. Here, with use of the MEMS switch **507r** as a typical example, the structure of the MEMS switch is described with reference to FIG. 12 and FIG. 13.

FIG. 13 is a perspective view of the MEMS switch **507r**. The MEMS switch **507r** includes a shutter **543** connected to an actuator **541**. The shutter **543** has opening portions. The actuator **541** has two flexible actuators **545**. One of sides of the shutter **543** is connected to the actuators **545**. The actuators **545** have a function of moving the shutter **543** in the lateral direction which is a direction parallel to a surface of the insulating layer **505**.

Each actuator **545** includes a movable electrode **551** connected to the shutter **543** and a structure body **549** and a movable electrode **555** connected to a structure body **553**. The movable electrode **555** is adjacent to the movable electrode **551**, and one end of the movable electrode **555** is connected to the structure body **553**, and the other end can be freely moved. The end portion of the movable electrode **555**, which can be freely moved, is bent so as to be closest to the connection portion of the movable electrode **551** and the structure body **549**.

The other side of the shutter **543** is connected to a spring **547** which has restoring force opposing force applied by the actuator **541**. The spring **547** is connected to a structure body **557**.

The structure bodies **549**, **553**, and **557** function as mechanical supports which lifts the shutter **543**, the actuators **545**, and the spring **547** in the vicinity of the surface of the insulating layer **505**.

An opening portion **559** surrounded by the reflective layer is provided below the shutter **543**. The opening portion **559** corresponds to the opening portion **503r** in FIG. 12.

The structure body **553** included in the MEMS switch **507r** is connected to the transistor which is not illustrated. Thus, a

given voltage can be applied to the movable electrode **555** connected to the structure body **553** through the transistor. The structure bodies **549** and **557** are each connected to a ground electrode (GND) with the reflective layer **503** illustrated in FIG. **12**. Therefore, a potential of the movable electrode **551** connected to the structure body **549** and a potential of the spring **547** connected to the structure body **557** are GND. Note that the structure bodies **549** and **557** may be electrically connected to a common electrode to which a given voltage can be applied.

When the voltage is applied to the movable electrode **555**, the movable electrode **551** and the movable electrode **555** are electrically drawn to each other due to a potential difference between the movable electrode **555** and the movable electrode **551**. As a result, the shutter **543** connected to the movable electrode **551** is drawn toward the structure body **553** and moves to the structure body **553** in the lateral direction. Since the movable electrode **551** has a function of a spring, when the voltage between the potential of the movable electrode **551** and the potential of the movable electrode **555** is removed, the movable electrode **551** releases the stress stored in the movable electrode **551** and pushes the shutter **543** back to the original position.

The manufacturing method of the MEMS switch **507r** is described below. A sacrificial layer with a predetermined shape is formed by a photolithography step over the insulating layer **505**. The sacrificial layer can be formed using an organic resin such as polyimide or acrylic, an inorganic insulating layer such as a silicon oxide layer, a silicon nitride layer, a silicon oxynitride layer, or a silicon nitride oxide layer, or the like.

Next, a conductive layer is formed over the sacrificial layer by a printing method, a sputtering method, an evaporation method, or the like, and then, is selectively etched, so that the MEMS switch **507** is formed. Alternatively, the MEMS switch **507** is formed by an inkjet method.

Next, the sacrificial layer is removed, whereby the MEMS switch **507r** which can be moved in a space can be formed. After that, the surface of the MEMS switch **507r** is preferably oxidized by oxygen plasma, thermal oxidation treatment, or the like, so that an oxide film is formed. Alternatively, an insulating film including alumina, silicon oxide, silicon nitride, silicon oxynitride, silicon nitride oxide, DLC (diamond-like carbon), or the like is preferably formed on the surface of the MEMS switch **507r** by an atomic layer deposition method or a CVD method. By providing the insulating film for the MEMS switch **507**, deterioration in characteristics of the MEMS switch **507** over time can be reduced.

The MEMS switch **507r** can be formed using metal such as aluminum, copper, nickel, chromium, titanium, molybdenum, tantalum, or neodymium or an alloy containing any of these. The MEMS switch **507** is formed to have a thickness greater than or equal to 100 nm and less than or equal to 5 μ m.

The light-blocking layer **513** provided for the second substrate **511** is provided to cover the reflective layer **503**.

The coloring layers **514r**, **514g**, and **514b** provided for the second substrate **511** can be formed in a manner similar to that of the coloring layer **337** described in Embodiment 2. Note that as the coloring layer, a coloring layer which transmits another color can be provided as appropriate.

Note that although not illustrated, the first substrate **501** and the second substrate **511** are fixed with a sealant to hold a certain space therebetween.

As the diffusion plate **515** and the luminance improvement sheet **517** illustrated in FIG. **12**, the diffusion plate **301** and the luminance improvement sheet described in Embodiment 2 can be used as appropriate.

As the backlight **519**, the backlight described in Embodiment 1 can be used.

With use of the backlight described in Embodiment 1, the color purity of light emitted from the second substrate **511** is increased. Therefore, color reproducibility of the display device can be increased. Since the display device including the MEMS switch has high use efficiency of light which is emitted from the backlight **519**, high contrast can be sufficiently obtained even when luminance of the backlight is decreased; thus, power consumption of the display device can be reduced.

Next, a circuit diagram and an operation method of the display device described in this embodiment are described with reference to FIG. **13** and FIG. **14**.

FIG. **14** is a circuit diagram of a display device described in this embodiment. A display device **600** includes a scan line driver circuit **601**, a signal line driver circuit **603**, and a pixel portion **605**. The pixel portion **605** is provided with scan lines **609** connected to the scan line driver circuit **601** and signal lines **611** connected to the signal line driver circuit **603**. In the pixel portion **605**, pixels **607** are arranged in matrix. The scan line driver circuit **601** is a circuit which makes the pixels **607** drive and has a function of outputting a plurality of display selection signals that are pulse signals. Further, the signal line driver circuit **603** has a function of generating a data voltage Vd in accordance with an inputted image signal and applying the generated data voltage Vd to the signal lines **611**. Each pixel **607** is provided with a transistor **613** in which a gate is connected to the scan line **609** and a first electrode is connected to the signal line **611**, a MEMS switch **615** in which a first terminal is connected to a second electrode of the transistor **613**, and a capacitor **617** in which a first electrode is connected to the second electrode of the transistor **613** and the first terminal of the MEMS switch **615**. A second terminal of the MEMS switch **615** and a second electrode of the capacitor **617** are connected to a ground electrode.

The transistor **613** controls the voltage applied to the MEMS switch **615**. The transistor described in Embodiment 2 can be used for the transistor **613**. Instead of the transistor, a diode or a metal insulator metal (MIM) may be used.

The MEMS switch **615** corresponds to the MEMS switch **507r** illustrated in FIG. **13**.

The MEMS switch **615** includes an actuator having two movable electrodes and a shutter. The two movable electrodes have capacitance different from each other.

The transistor **613** is connected to the movable electrode **555** having lower capacitance with the structure body **553** in the MEMS switch **615**. The movable electrode **551** in the MEMS switch **507** is connected to the shutter **543** with a large area and thus has high capacitance and is connected to a common electrode or a ground electrode with the structure body **549**. The spring **547** is connected to the common electrode or the ground electrode with the structure body **557**.

A writing voltage Vwe is sequentially applied to the scan lines **609**, so that the transistors **613** are turned on in sequence. The data voltage Vd is applied to the selected signal line **611**. The data voltage Vd is written to the MEMS switch **615** and the capacitor **617** which are connected to the transistor **613** that is on. Thus, a potential difference is generated between the movable electrode **555** and the shutter **543**. Due to generation of the potential difference, the shutter is electrically drawn toward the movable electrode **555**, moves, and does not overlap with an opening portion of the pixel portion; thus, light from the backlight passes through the opening portion.

In a display device of an analog driving method, the data voltage Vd is applied to the signal lines **611** in accordance with desired luminance of the pixels **607**. The moving dis-

tance of the shutter in the MEMS switch **615** depends on the data voltage V_d . In accordance with the moving distance of the shutter, an area where the opening portion of the pixel portion overlaps with the opening portion of the shutter varies or the opening portion of the pixel portion does not overlap with the opening portion of the shutter; thus, the amount of light, which passes through the opening portion, from the backlight varies.

In the display device of a digital driving method, as the data voltage V_d , a voltage that is lower than the voltage at which the actuator of the MEMS switch **615** operates (the operation threshold voltage) or higher than the operation threshold voltage is applied. With application of the data voltage V_d that is higher than the operation threshold voltage, the shutter of the MEMS switch **615** moves, and light from the backlight is transmitted through the opening portion of the pixel portion.

The voltage applied to the signal line **611** is held in the capacitor **617** of the pixel **607** even after the application of the wiring voltage V_{we} is stopped. The voltage of the capacitor **617** is substantially stored until the whole video frame has been written or new data is written to the signal line **611**. Thus, the number of times of writing can be minimized, and power consumption of the display device can be reduced.

Note that in this embodiment, the circuit diagram in which one transistor is connected to the MEMS switch **615** is illustrated, but the circuit configuration is not limited to this, and transistors can be provided as appropriate.

The display device including the MEMS switch has high use efficiency of light emitted from the backlight; thus, sufficiently high contrast can be obtained even when luminance of the backlight is decreased. As a result, power consumption of the display device can be reduced.

Embodiment 4

A display device of one embodiment of the present invention can be applied to a variety of electronic devices. Examples of electronic devices include a television device (also referred to as a TV or a television receiver). In addition, a display device of one embodiment of the present invention can be applied to indoor digital signage, public information display (PID), advertisements in vehicles such as a train, or the like. In particular, since the display device of one embodiment of the present invention can improve color purity, the use of the display device as the above electronic devices is effective in obtaining color reproducibility. Examples of electronic devices in which the display device of one embodiment of the present invention is used are illustrated in FIGS. **15A** and **15B**.

FIG. **15A** illustrates an example of a television device. In a television device **1000**, a display portion **1002** is incorporated in a housing **1001**. Images can be displayed on the display portion **1002**. Here, the housing **1001** is supported by a housing **1004**. In addition, the television device **1000** is provided with a speaker **1003**, operation keys **1005** (including a power switch or an operation switch), a connection terminal **1006**, a sensor **1007** (having a function of measuring force, displacement, position, speed, distance, light, temperature, sound, time, electric field, current, voltage, electric power, or infrared ray), a microphone **1008**, and the like.

The television device **1000** can be operated with the operation switch or a separate remote controller **1010**. With operation keys **1009** provided in the remote controller **1010**, channels or volume can be controlled, whereby an image displayed on the display portion **1002** can be controlled. The remote controller **1010** may include a display portion **1011** for displaying data output from the remote controller **1010**.

Note that the television device **1000** is provided with a receiver, a modem, and the like. A general television broadcast can be received with the receiver. Moreover, when the display device is connected to a communication network with or without wires via the modem, one-way (from a sender to a receiver) or two-way (between a sender and a receiver or between receivers) information communication can be performed.

FIG. **15B** illustrates an example of digital signage. For example, digital signage **2000** includes two housings, a housing **2002** and a housing **2004**. The housing **2002** includes a display portion **2006** and two speakers, a speaker **2008** and a speaker **2010**. In addition, the digital signage **2000** may be provided with a sensor so as to operate in a following manner: an image is not displayed when a person is not close to the digital signage or the like.

The display device of one embodiment of the present invention can be used for the display portion **1002** in the television device **1000** and the display portion **2006** in the digital signage **2000** and has an advantage of improving color purity. Thus, color reproducibility of the television device **1000** and the digital signage **2000** can be increased.

Note that this embodiment can be implemented in free combination with any of the other embodiments.

This application is based on Japanese Patent Application serial no. 2010-238723 filed with Japan Patent Office on Oct. 25, 2010, the entire contents of which are hereby incorporated by reference.

What is claimed is:

1. A light-emitting element unit comprising:

a board;

a light-emitting element chip provided over the board;

a micro optical resonator provided at a periphery of the light-emitting element chip; and

a phosphor layer covering at least the light-emitting element chip,

wherein the phosphor layer is provided between the light-emitting element chip and the micro optical resonator, and

wherein the micro optical resonator comprises a reflective layer, a semi-transmissive semi-reflective layer facing the reflective layer and a light-transmitting layer sandwiched therebetween.

2. The light-emitting element unit according to claim 1, wherein the semi-transmissive semi-reflective layer covers a top surface and a side surface of the light-transmitting layer.

3. The light-emitting element unit according to claim 2, wherein a light path length L between the reflective layer and the semi-transmissive semi-reflective layer is represented by a formula, $L=(2m+1)\lambda/4n$, and

wherein the m indicates an integer, the λ indicates a wavelength, and the n indicates a refractive index of the light-transmitting layer.

4. The light-emitting element unit according to claim 3, wherein the λ is 430 nm to 490 nm.

5. The light-emitting element unit according to claim 3, wherein the λ is 490 nm to 550 nm.

6. The light-emitting element unit according to claim 3, wherein the λ is 550 nm to 590 nm.

7. The light-emitting element unit according to claim 3, wherein the λ is 640 nm to 770 nm.

8. The light-emitting element unit according to claim 2, wherein the light-transmitting layer comprises a plurality of layers which are stacked.

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9. The light-emitting element unit according to claim 1, wherein the phosphor layer covers the micro optical resonator.

10. The light-emitting element unit according to claim 1, further comprising an organic resin layer covering the phosphor layer, wherein the organic resin layer transmits a light, and wherein a shape of the organic resin layer is a convex shape.

11. The light-emitting element unit according to claim 1, wherein the micro optical resonator does not overlap with the light-emitting element chip.

12. A display device comprising:

a substrate;

a module including a light-emitting element unit provided over the substrate;

a diffusion plate overlapping with the module;

a first polarizing plate overlapping with the diffusion plate;

a liquid crystal panel overlapping with the first polarizing plate; and

a second polarizing plate overlapping with the liquid crystal panel,

the light-emitting element unit comprising:

a board;

a light-emitting element chip provided over the board;

a micro optical resonator provided at a periphery of the light-emitting element chip; and

a phosphor layer covering at least the light-emitting element chip,

wherein the phosphor layer is provided between the light-emitting element chip and the micro optical resonator,

wherein the micro optical resonator comprises a reflective layer, a semi-transmissive semi-reflective layer facing the reflective layer and a light-transmitting layer sandwiched therebetween, and

wherein the liquid crystal panel includes a coloring layer.

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13. The display device according to claim 12, wherein an optical member is provided between the diffusion plate and the first polarizing plate.

14. The display device according to claim 12,

wherein the semi-transmissive semi-reflective layer covers a top surface and a side surface of the light-transmitting layer.

15. The display device according to claim 14, wherein a light path length L between the reflective layer and the semi-transmissive semi-reflective layer is represented by a formula, $L = (2m+1)\lambda/4n$, and

wherein the m indicates an integer, the λ indicates a wavelength, and the n indicates a refractive index of the light-transmitting layer.

16. The display device according to claim 15, wherein the λ is 430 nm to 490 nm.

17. The display device according to claim 15, wherein the λ is 490 nm to 550 nm.

18. The display device according to claim 15, wherein the λ is 550 nm to 590 nm.

19. The display device according to claim 15, wherein the λ is 640 nm to 770 nm.

20. The display device according to claim 14, wherein the light-transmitting layer comprises a plurality of layers which are stacked.

21. The display device according to claim 12, wherein the phosphor layer covers the micro optical resonator.

22. The display device according to claim 12, further comprising an organic resin layer covering the phosphor layer, wherein the organic resin layer transmits a light, and wherein a shape of the organic resin layer is a convex shape.

23. The display device according to claim 12, wherein the micro optical resonator does not overlap with the light-emitting element chip.

* * * * *

专利名称(译)	发光元件单元和显示装置		
公开(公告)号	US9306129	公开(公告)日	2016-04-05
申请号	US13/277417	申请日	2011-10-20
[标]申请(专利权)人(译)	株式会社半导体能源研究所		
申请(专利权)人(译)	半导体能源研究所有限公司.		
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发明人	YAMAZAKI, SHUNPEI HIRAKATA, YOSHIHARU		
IPC分类号	G02F1/1335 H01L33/50 H01L33/46 H01L33/48		
CPC分类号	H01L33/50 H01L33/465 G02F1/133514 G02F1/133621 H01L33/486 H01L2224/48227 H01L2224/48465 H01L2924/07811 H01L2924/1461 H01L2924/3025 H01L2924/00 H01L33/505 G02F1/133603 H01L25/0753 H01L33/54 H01L33/56 H01L33/62		
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审查员(译)	KIM , RICHARD		
优先权	2010238723 2010-10-25 JP		
其他公开文献	US20120099048A1		
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摘要(译)

提供一种发光元件单元，其可以改善从滤色器发出的光的色纯度。提供了一种具有高色纯度和高色彩再现性的显示装置。发光元件单元包括布线板，设置在布线板上的发光元件芯片，设置在布线板上和发光元件芯片周边的微光学谐振器，以及覆盖该布线板的荧光体层。发光元件芯片和微光学谐振器。该显示装置包括具有着色层的显示面板和具有该发光元件单元的背光模块。显示面板的示例包括：液晶面板；显示面板包括设置在第一基板上的开口部分，在横向方向上在开口部分上方移动的MEMS，以及在与开口部分对应的部分中设置有着色层的第二基板。

